



NM25WD40A Datasheet

1.8/3.3V 4Mbit Serial Flash Memory with Standard, Dual SPI



NM25WD40A SPI NOR Flash Datasheet

DS013 (v1.0)

Product Specification

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1. Features

- **4Mbit SPI NOR Flash**
 - Totally 512K bytes
 - 256-byte Page Program
 - 0.5KB/4KB Sector/32KB Block/64KB Block/Chip Erase
- **Protocols Supported**
 - Standard SPI: SCLK, CS#, SI, SO, WP#
 - Dual SPI: SCLK, CS#, IO0, IO1, WP#
- **Single Supply Voltage**
 - Full voltage range: 1.65V~3.6V
- **High Performance**
 - 104MHz maximum clock frequency
 - Dual I/O data throughput up to 208Mbit/s
 - Page Program: 0.8ms typical
 - 0.5KB Sector Erase: 2.9ms typical
 - Sector Erase: 2.9ms typical
 - 32KB Block Erase: 2.9ms typical
 - 64KB Block Erase: 2.9ms typical
 - Chip Erase: 5.7ms typical
- **Software and Hardware Write Protection**
 - Protection of portion or all of memory space
 - Protection enabled/disabled by WP#
 - Top/Bottom protection mechanisms
- **Low Power Consumption**
 - 10uA Standby current
 - Maximum 4.8mA active current
 - Typical 0.1uA power down current
- **Advanced Security Features**
 - 3*512-byte Security Registers with OTP lock
 - 128-bit Unique ID for each device
- **Temperature Range**
 - Commercial: -40°C to +85°C
 - Industrial: -40°C to +105°C
- **Endurance of 100,000 Program/Erase Cycles**
- **Data Retention of 20 Years**
- **Industry Standard Packaging**
 - SOP8, SOP16
 - DIP8
 - WSON8
 - TFBGA-24

2. General Description

The NM25WD40A of non-volatile flash memory device supports the standard Serial Peripheral Interface (SPI). Traditional SPI single bit serial input and output (Single I/O or SIO) is supported as well as optional two bit (Dual I/O or DIO) serial protocols.

The NM25WD40A support the standard Serial Peripheral Interface (SPI), Dual I/O SPI : Serial Clock, Chip Select, Serial Data I/O0 (DI), I/O1 (DO). The clock frequencies are supported allowing equivalent clock rates of 208MHz (104MHz x 2) for Dual I/O. These transfer rates can outperform standard synchronous 8 and 16-bit Parallel Flash memories

Additionally, the device supports JEDEC standard manufacturer and device ID and SFDP Register, a 128-bit Unique Serial Number and three 512-Bytes Security Registers. The NM25WD40A provides an ideal storage solution for systems with limited space, signal connections, and power. These memories' flexibility and performance is better than ordinary serial flash devices. They are ideal for code shadowing to RAM, executing code directly (XIP), and storing reprogrammable data.

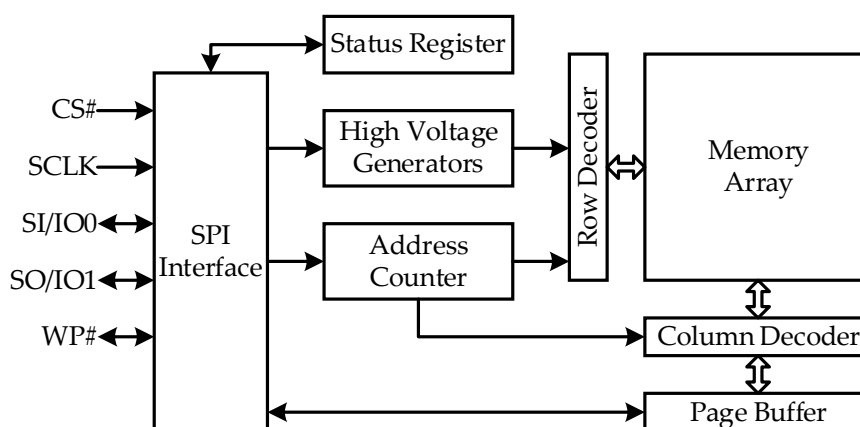


Figure 1: NM25WD40A SPI Flash Block Diagram

3. Pin Configuration

The NM25WD40A device has the following pin configurations.

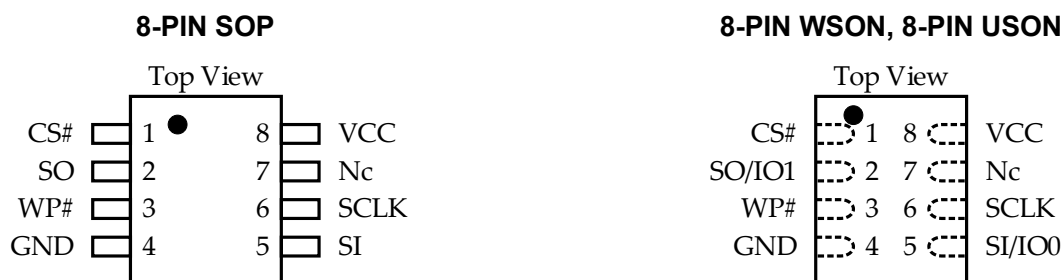


Figure 2: Pin Map

4. Pin Description

The NM25WD40A SPI Flash memory device operates with a wide supply range from 1.65V to 3.6V.

Table 1: Pin Definitions

Signal	Direction	Description
CS#	Input	Chip Select, active low
SCLK	Input	Clock Input
SI/IO0	Input/Output	Serial Data Input in standard SPI; IO0 in Dual
SO/IO1	Input/Output	Serial Data Output in standard SPI; IO1 in Dual
WP#	-	Activ Write Protect in standard SPI
Nc	-	Not Connection
VCC	-	Power Supply
GND	-	GND

4.1. Chip Select (CS#)

The Chip Select (CS#) pin enables and disables device operations.

When CS# is high, the device is deselected and all data output pins are at high impedance state; the device is in standby mode with standby level of power consumption if Write Status Register, program or erase operations are absent.

When CS# is low, the device is selected, available for incoming commands.

4.2. Clock Input (SCLK)

The clock input provides a reference of the synchronization of the SPI interface. All inputs are latched on the rising edge of SCLK, while all data shifts out on its falling edge.

4.3. Serial Input (SI/IO0)

Serial input is a unidirectional pin in Standard SPI mode, which is the input for all commands, data and address. In Dual SPI modes, SI functions as bidirectional IO0, which receives command, address and data as an input, and shifts out data as an output.

4.4. Serial Output (SO/IO1)

SO is unidirectional in Standard SPI mode for the output of all internal status and data. In Dual SPI modes, SO functions as bidirectional IO1, which receives data and address, and shifts out data.

4.5. Write Protect

The Write Protect (WP#) pin can be used to prevent the Status Register from being written. Used in conjunction with the Status Register's Block Protect (BP0, BP1 and BP2, TB, SEC, CMP) bits and Status Register Protect (SRP) bits, a portion or the entire memory array can be hardware protected.

5. Memory Organization and Operations

The NM25WD40A utilizes a variety of registers and memory array to store control information and user data, including: Identification, Status Register, Security Register, SFDP register, main memory array.

5.1. Identification

Table 2: Identification Definitions

Command	Comments	Manufacture ID (MID7 ~ MID0)	Memory Type (ID15 ~ ID8)	Memory Density (ID7 ~ ID0)	Device ID (ID7 ~ ID0)
----	----	94h	32h	13h	12h
9Fh	Read Identification	✓	✓	✓	----
90h/92h/94h	Read Manufacturer / Device ID	✓	----	----	✓
ABh	Read Device ID	----	----	----	✓

5.2. Status Register

The Read and Write Status Registers commands can be used to provide status and control of the flash memory device. Status Register-1 (SR1) and Status Register-2 (SR2) can be used to provide status on the availability of the flash memory array, whether the device is write enabled or disabled, the state of write protection, Security Register lock status.

Table 3: Status Register 2 (SR2)

Bit	S15	S14	S13	S12	S11	S10	S9	S8
Name	Reserved	CMP	LB3	LB2	LB1	Reserved	Reserved	SRP1
R/W	-	R/W	R/W	R/W	R/W	-	-	R/W

The SR2 register is read by 35h and written by 31h commands.

Table 4: Status Register 1 (SR1)

Bit	S7	S6	S5	S4	S3	S2	S1	S0
Name	SRP0	BP4	BP3	BP2	BP1	BP0	WEL	WIP
R/W	R/W	R/W	R/W	R/W	R/W	R/W	R	R

The SR1 register is read by 05h and written by 01h commands.

5.2.1.WIP Bit

Write In Progress Bit(WIP) indicates whether a WRSR, program or erase operation is in progress.

0 = device is idle

1 = device is busy in WRSR, program or erase operation

5.2.2.WEL Bit

Write Enable Latch Bit(WEL) indicates whether the device is ready to accept a WRSR, program or erase command.

0 = WRSR, program or erase command is not accepted

1 = WRSR, program or erase command is allowed

WEL is reset by:

- (1) Power up;
- (3) Write Disable (WRDI, 04h) command;
- (2) Completion of WRSR, program or erase operations;
- (4) Software Reset (66h+99h) command.

5.2.3.BP4, BP3, BP2, BP1, BP0 Bits

BP4 through BP0 are Block Protect bits. BP bits in combination with CMP bit define the protect scheme of the main memory array.

For details, see Table 11 and Table 12.

5.2.4.The Status Register Protect (SRP1, SRP0)

The Status Register Protect bits (SRP1 and SRP0) are non-volatile read / write bits in the Status Register (SR2[0] and SR1[7]). The SRP bits control the method of write protection: software protection, hardware protection, power supply lock-down, or one time programmable (OTP) protect .For details, see Table10.

5.2.5.LB3, LB2, LB1 Bits

LB3, LB2 and LB1 are the Lock Bits for Security Registers 3, 2 and 1, respectively.

0 = The corresponding Security Register can be programmed/erased.

1 = The corresponding Security Register is protected permanently.

LB3 through LB1 are OTP bits. Upon device delivery, they are default to 0. Programming from 0 to 1 is permanent.

LB3, LB2 and LB1 are can only be written by 06h command, but not can be written by 05h command.

5.2.6.CMP Bit

Complement Protect Bit(CMP), which in conjunction with Block Protect bits (BP4 through BP0) determines the protection scheme of the main memory array.

For details, see Table 11 and Table 12.

5.3. Security Register

Security Registers are three 512-byte registers that can be individually protected by OTP programmable LB bits. Once a LB bit is set to 1, the corresponding Security Register becomes permanently locked and all program or erase operations are ignored.

These registers can be individually erased, programmed or read using 44h, 42h or 48h commands; they may be used as storage for security or other important information separately from the main memory array.

Table 5: Security Register Address Distribution

Security Register	A23-A16	A15-A12	A11-A9	A8-A0
Security Register #1	00h	0001	0	Byte Address
Security Register #2	00h	0010	0	Byte Address
Security Register #3	00h	0011	0	Byte Address

5.4. SFDP Register

The NM25WD40A features a 256-byte Serial Flash Discoverable Parameter (SFDP) register. It provides a means to interrogate flash device characteristics and make appropriate adjustments while accessing the device.

The concept of SFDP Register definitions is similar to the JEDEC JESD216 standard (April 2011).

5.4.1.SFDP Header Information

Table 6: Signature and Parameter Identification Data Values

Description	Comment	Addr ¹	Bits ²	Data ³	Data ⁴
SFDP Signature	Fixed:50444653h	00h	[07:00]	53h	53h
		01h	[15:08]	46h	46h
		02h	[23:16]	44h	44h
		03h	[31:24]	50h	50h
SFDP Minor Revision Number	Start from 00h	04h	[07:00]	08h	08h
SFDP Major Revision Number	Start from 01h	05h	[15:08]	01h	01h
Number of Parameters Headers	Start from 00h	06h	[23:16]	01h	01h
Unused	Contains 0xFFh and can never be changed	07h	[31:24]	FFh	FFh
ID number (JEDEC)	00h: A JEDEC specified header	08h	[07:00]	00h	00h
Parameter Table Minor Revision Number	Start from 0x00h	09h	[15:08]	07h	07h
Parameter Table Major Revision Number	Start from 0x01h	0Ah	[23:16]	01h	01h
Parameter Table Length (in double word)	Number of DWORDs in the Parameter table	0Bh	[31:24]	10h	10h
Parameter Table Pointer (PTP)	First address of JEDEC Flash Parameter table	0Ch	[07:00]	30h	30h
		0Dh	[15:08]	00h	00h
		0Eh	[23:16]	00h	00h
Unused	Contains 0xFFh and can never be changed.	0Fh	[31:24]	FFh	FFh
ID Number (NeuMem Manufacturer ID)	Indicates NeuMem manufacturer ID	10h	[07:00]	94h	94h
Parameter Table Minor Revision Number	Start from 0x00h	11h	[15:08]	00h	00h
Parameter Table Major Revision Number	Start from 0x01h	12h	[23:16]	01h	01h
Parameter Table Length (in double word)	Number of DWORDs in the Parameter table	13h	[31:24]	03h	03h
Parameter Table Pointer (PTP)	First address of NeuMem Flash Parameter table	14h	[07:00]	70h	70h
		15h	[15:08]	00h	00h
		16h	[23:16]	00h	00h
Unused	Contains 0xFFh and can never be changed	17h	[31:24]	FFh	FFh

5.4.2.Parameter Table (0)

Table 7: Parameter Table (0): JEDEC Flash Parameter Tables

Description	Comment	Addr	Bits	Data	Data
Block/Sector Erase Size	00: Reserved; 01: 4KB Erase; 10: Reserved; 11: do not support 4KB erase	30h	[01:00]	01b	E5h
Write Granularity	0: 1Byte, 1: 64Byte or larger		[02]	1b	
Write Enable Instruction Required for	0: Nonvolatile status bit		[03]	0b	

Writing to Volatile Status Register	1: Volatile status bit				
Write Enable Opcode Select for Writing to Volatile Status Registers	0: Use 50h Opcode; 1: Use 06h Opcode. Note: If target flash status register is Nonvolatile, then bits 3 and 4 must be set to 00b.		[04]	0b	
Unused	Contains 111b and can never be changed		[07:05]	111b	
4KB Erase Opcode		31h	[15:08]	20h	20h
(1-1-2) Fast Read	0=Not supported 1=Supported	32h	[16]	1b	91h
Number of Address Bytes used in addressing flash array	00: 3-Byte only; 01: 3- or 4-Byte; 10: 4-Byte only; 11: Reserved		[18:17]	00b	
Double Transfer Rate (DTR) clocking	0=Not supported 1=Supported		[19]	0b	
(1-2-2) Fast Read	0=Not supported 1=Supported		[20]	1b	
(1-4-4) Fast Read	0=Not supported 1=Supported		[21]	0b	
(1-1-4) Fast Read	0=Not supported 1=Supported		[22]	0b	
Unused	----		[23]	1b	
Unused	----	33h	[31:24]	FFh	FFh
Flash Memory Density		37h: 34h	[31:00]	003F_FFFFh	
(1-4-4) Fast Read Number of Wait states	0_0000b: Wait states (dummy clocks) not supported	38h	[04:00]	0_0100 b	00h
(1-4-4) Fast Read Number of Mode Bits	000b: Mode Bits not supported		[07:05]	010b	
(1-4-4) Fast Read Opcode		39h	[15:08]	EBh	EBh
(1-1-4) Fast Read Number of Wait states	0_0000b: Wait states (Dummy Clocks) not supported	3Ah	[20:16]	0_1000 b	00h
(1-1-4) Fast Read Number of Mode Bits	000b: Mode Bits not supported		[23:21]	000b	
(1-1-4) Fast Read Opcode		3Bh	[31:24]	6Bh	6Bh
(1-1-2) Fast Read Number of Wait states	0_0000b: Wait states (Dummy Clocks) not supported	3Ch	[04:00]	0_1000 b	08h
(1-1-2) Fast Read Number of Mode Bits	000b: Mode Bits not supported		[07:05]	000b	
(1-1-2) Fast Read Opcode		3Dh	[15:08]	3Bh	3Bh
(1-2-2) Fast Read Number of Wait states	0_0000b: Wait states (Dummy Clocks) not supported	3Eh	[20:16]	0_0000 b	40h
(1-2-2) Fast Read Number of Mode Bits	000b: Mode Bits not supported		[23:21]	010b	
(1-2-2) Fast Read Opcode		3Fh	[31:24]	BBh	BBh
(2-2-2) Fast Read	0: Not supported	40h	[00]	0b	EEh

	1: Supported				
Unused	----		[03:01]	111b	
(4-4-4) Fast Read	0: Not supported 1: Supported		[04]	0b	
Unused	----		[07:05]	111b	
Unused	----	43h: 41h	[31:08]	0xFFh	0xFFh
Unused	----	45h: 44h	[15:00]	0xFFh	0xFFh
(2-2-2) Fast Read Number of Wait states	0_0000b: Wait states (Dummy Clocks) not supported	46h	[20:16]	00000b	00h
(2-2-2) Fast Read Number of Mode Bits	000b: Mode Bits not supported		[23:21]	000b	
(2-2-2) Fast Read Opcode		47h	[31:24]	FFh	FFh
Unused	----	49h: 48h	[15:00]	0xFFh	0xFFh
(4-4-4) Fast Read Number of Wait states	0_0000b: Wait states (Dummy Clocks) not supported	4Ah	[20:16]	0_0000b	00h
(4-4-4) Fast Read Number of Mode Bits	000b: Mode Bits not supported		[23:21]	000b	
(4-4-4) Fast Read Opcode		4Bh	[31:24]	52h	52h
Sector Type 1 Size	0x00b: Sector type doesn't exist N: sector/block size = 2 ^N bytes	4Ch	[07:00]	0Ch	0Ch
Sector Type 1 erase Opcode		4Dh	[15:08]	20h	20h
Sector Type 2 Size	0x00b: Sector type doesn't exist N: sector/block size = 2 ^N bytes	4Eh	[23:16]	0Fh	0Fh
Sector Type 2 erase Opcode		4Fh	[31:24]	52h	52h
Sector Type 3 Size	0x00b: Sector type doesn't exist N: sector/block size = 2 ^N bytes	50h	[07:00]	10h	10h
Sector Type 3 erase Opcode		51h	[15:08]	D8h	D8h
Sector Type 4 Size	0x00b: Sector type doesn't exist N: sector/block size = 2 ^N bytes	52h	[23:16]	00h	00h
Sector Type 4 erase Opcode		53h	[31:24]	FFh	FFh

5.4.3. Parameter Table (1)

Table 8: Parameter Table (1): NeuMem Flash Parameter Tables

Description	Comment	Addr	Bits	Data	Data
Vcc Supply Maximum Voltage	2000h=2.000V 2700h=2.700V 3600h=3.600V	61h: 60h	[15:00]	3600h	3600h
Vcc Supply Minimum Voltage	1650h=1.650V 2250h=2.250V 2350h=2.350V 2700h=2.700V	63h: 62h	[31:16]	1650h	1650h

Hardware Reset# pin	0 = Not supported 1 = Supported	65h: 64h	[00]	0b	F99Eh
Hardware Hold# pin	0 = Not supported 1 = Supported		[01]	0b	
Deep Power Down Mode	0 = Not supported 1 = Supported		[02]	1b	
Software Reset	0 = Not supported 1 = Supported		[03]	1b	
Software Reset Opcode	(Reset Enable 66h should be issued before Reset Opcode)		[11:04]	99h	
Program Suspend/Resume	0 = Not supported 1 = Supported		[12]	0b	
Erase Suspend/Resume	0 = Not supported 1 = Supported		[13]	0b	
Unused	----		[14]	1b	
Wrap-Around Read mode	0 = Not supported 1 = Supported		[15]	0b	
Wrap-Around Read mode Opcode		66h	[23:16]	FFh	FFh
Wrap-Around Read data length	08h: Support 8B wrap-around read 16h: 8B & 16B 32h: 8B & 16B & 32B 64h: 8B & 16B & 32B & 64B	67h	[31:24]	64h	64h
Individual block lock	0 = Not supported 1 = Supported	6Bh: 68h	[00]	0b	EBFCh
Individual block lock bit (Volatile/Nonvolatile)	0 = Volatile 1 = Nonvolatile		[01]	0b	
Individual block lock Opcode			[09:02]	FFh	
Individual block lock Volatile protect bit default protect status	0 = Protect 1 = Unprotect		[10]	0b	
Secured OTP	0 = Not supported 1 = Supported		[11]	1b	
Read Lock	0 = Not supported 1 = Supported		[12]	0b	
Permanent Lock	0 = Not supported 1 = Supported		[13]	1b	
Unused	----		[15:14]	11b	
Unused	----		[31:16]	FFFFh	FFFFh

5.5. Main Array

5.5.1. Address Space Distribution of Main Array

Table 9: NM25WD40A Memory Organization

Each device has	Each block has	Each sector has	Each page has	
512K	64K/32K	4K	256	Bytes
2K	256/128	16	-	Pages
128	16/8	-	-	Sectors
8/16	-	-	-	Blocks

Table 10: NM25WD40A Address Distribution

Block	Sector	Address Range	
Block7	127	07F000H	07FFFFH
			
	112	070000H	070FFFH
Block6	111	06F000H	06FFFFH
			
	96	060000H	060FFFH
.....			
			
			
.....			
			
			
Block2	47	02F000H	02FFFFH
			
	32	020000H	020FFFH
Block1	31	01F000H	01FFFFH
			
	16	010000H	010FFFH
Block0	15	00F000H	00FFFFH
			
	0	000000H	000FFFH

6. SPI Operation

6.1. Standard SPI

Standard SPI has a four signal bus: CS#, SCLK, SI and SO. Both mode 0 and 3 are supported. Input data is latched on the rising edge of SCLK and data shifts out on the falling edge of SCLK.

6.2. Dual SPI

The device supports Dual SPI operations for the following commands:

"Dual Output Fast Read" (3Bh);

"Dual I/O Fast Read" (BBh);

"Dual Input Page Program (A2h)"

"Read Manufacture ID / Device ID Dual I/O" (92h).

During these commands, SI and SO pins become IO0 and IO1. Data is transferred using IO0 and IO1, doubling the throughput of Standard SPI mode.

7. Data Protection

As a nonvolatile memory device the NM25WD40A may suffer from the compromise of data integrity in the event of noise and other adverse system conditions. To improve the robustness of the device, certain methods are adopted to protect the data from inadvertent WRSR, program or erase operations.

7.1. Write Protect Features

NM25WD40A offers the following protection schemes.

- (1) The device is reset when Vcc is below threshold.
- (2) Write is disabled for a duration after device is power-up.
- (3) Prior to WRSR, program or erase operations, a Write Enable (WREN) command is needed to set WEL bit to 1; after these operations are complete, the WEL bit returns to 0.

This mechanism ensures that the memory content can be changed only after specific command sequence is successfully completed.

- (4) Software Protection Mode: The CMP, BP4, BP3, BP2, BP1 and BP0 bits define the address space in the main memory array that is under protection. The protected area can only be read out; program or erase operations to protected area are ignored.

For details, see Table 11 and Table 12.

- (5) Hardware Protection Mode: WP# pin and SRP0,SRP1 bit protect Status Register bits from modifications. For details, see Table 10.
- (6) While in Deep Power-Down Mode, the device ignores all commands except Release from Deep Power-Down Mode (ABh). This protects the device from all WRSR, program or erase commands.

7.2. Status Register Protection

SRP0 and SRP1 bit in the Status Register and WP# pin provide protection for the Status Register itself.

Table 11: Status Register Protection Scheme

SRP1	SRP0	WP#	Protection Scheme	Description
0	0	X	Software Protected	WP# pin has no control. SR1 and SR2 can be written to after a Write Enable command, WEL=1.
0	1	0	Hardware Protected	When WP# pin is low the SR1 and SR2 are locked and cannot be written.
0	1	1	Hardware Unprotected	When WP# pin is high SR1 and SR2 are unlocked and can be written to after a Write Enable command, WEL=1.
1	0	X	Power Supply Lock Down	SR1 and SR2 are protected and cannot be written to again until the next power-down, power-up cycle.
1	1	X	One Time Program	SR1 and SR2 are permanently protected and can't be written.

Notes:

- (1) When SRP1, SRP0 = (1, 0), a power-down, power-up, or Software Reset cycle will change SRP1, SRP0 to (0, 0)

state.

7.3. Main Memory Array Protection

A combination of Status Register bits define the area space of the memory array that is protected from program and erase operations. A program operation targeted at a page address that is under protection is not executed. For erase operations, if any address location within the designated target area is protected then the command is not executed.

7.3.1.CMP=0

Table 12: NM25WD40A Memory Protection pattern (CMP=0)

Status Register					Block Protection (CMP=0)			
BP4	BP3	BP2	BP1	BP0	Blocks	Address Range	Density	Portion
x	x	0	0	0	None	None	None	None
0	0	0	0	1	7	070000h – 07FFFFh	64KB	Upper 1/8
0	0	0	1	0	6 and 7	060000h – 07FFFFh	128KB	Upper 1/4
0	0	0	1	1	4 thru 7	040000h – 07FFFFh	256KB	Upper 1/2
0	1	0	0	1	0	000000h – 00FFFFh	64KB	Lower 1/8
0	1	0	1	0	0 and 1	000000h – 01FFFFh	128KB	Lower 1/4
0	1	0	1	1	0 thru 3	000000h – 03FFFFh	256KB	Lower 1/2
0	x	1	x	x	0 thru 7	000000h – 07FFFFh	512KB	ALL
1	0	0	0	1	7	07F000h – 07FFFFh	4KB	Upper 1/128
1	0	0	1	0	7	07E000h – 07FFFFh	8KB	Upper 1/64
1	0	0	1	1	7	07C000h – 07FFFFh	16KB	Upper 1/32
1	0	1	0	x	7	078000h – 07FFFFh	32KB	Upper 1/16
1	0	1	1	0	7	078000h – 07FFFFh	32KB	Upper 1/16
1	1	0	0	1	0	000000h – 000FFFh	4KB	Lower 1/128
1	1	0	1	0	0	000000h – 001FFFh	8KB	Lower 1/64
1	1	0	1	1	0	000000h – 003FFFh	16KB	Lower 1/32
1	1	1	0	x	0	000000h – 007FFFh	32KB	Lower 1/16
1	1	1	1	0	0	000000h – 007FFFh	32KB	Lower 1/16
1	x	1	1	1	0 thru 7	000000h – 07FFFFh	512KB	ALL

Notes:

- (1) X = don't care
- (2) If any Erase or Program command specifies a memory region that contains protected data portion, this command will be ignored.

7.3.2.CMP=1

The CMP bit offers more flexibility in memory protection, as is shown below.

Table 13: NM25WD40A Memory Protection pattern (CMP=1)

Status Register					Block Protection (CMP=1)			
BP4	BP3	BP2	BP1	BP0	Blocks	Address Range	Density	Portion
x	x	0	0	0	0 thru 7	000000h – 07FFFFh	512KB	ALL

0	0	0	0	1	0 thru 6	000000h – 06FFFFh	448KB	Lower 7/8
0	0	0	1	0	0 thru 5	000000h – 05FFFFh	384KB	Lower 3/4
0	0	0	1	1	0 thru 3	000000h – 03FFFFh	256KB	Lower 1/2
0	1	0	0	1	1 thru 7	010000h – 07FFFFh	448KB	Upper 7/8
0	1	0	1	0	2 thru 7	020000h – 07FFFFh	384KB	Upper 3/4
0	1	0	1	1	4 thru 7	040000h – 07FFFFh	256KB	Upper 1/2
0	x	1	x	x	NONE	NONE	NONE	NONE
1	0	0	0	1	0 thru 7	000000h – 07EFFFh	508KB	Lower 127/128
1	0	0	1	0	0 thru 7	000000h – 07DFFFh	504KB	Lower 63/64
1	0	0	1	1	0 thru 7	000000h – 07BFFFh	496KB	Lower 31/32
1	0	1	0	x	0 thru 7	000000h – 077FFFh	480KB	Lower 15/16
1	0	1	1	0	0 thru 7	000000h – 077FFFh	480KB	Lower 15/16
1	1	0	0	1	0 thru 7	001000h – 07FFFFh	508KB	Upper 127/128
1	1	0	1	0	0 thru 7	002000h – 07FFFFh	504KB	Upper 63/64
1	1	0	1	1	0 thru 7	004000h – 07FFFFh	496KB	Upper 31/32
1	1	1	0	x	0 thru 7	008000h – 07FFFFh	480KB	Upper 15/16
1	1	1	1	0	0 thru 7	008000h – 07FFFFh	480KB	Upper 15/16
1	x	1	1	1	NONE	NONE	NONE	NONE

Notes:

- (1) X = don't care
- (2) If any Erase or Program command specifies a memory region that contains protected data portion, this command will be ignored.

8. Command Definitions

All commands, addresses and data are shifted in and out of the device, beginning with the MSB of the command opcode. All inputs are latched into the device on SCLK rising edge, while all outputs are shifted out on SCLK falling edge.

Every command sequence starts with a one-byte command code. Depending on the command, the command code might be followed by address bytes, data bytes, dummy bytes, or a combination. CS# must be driven high after the last bit of the command sequence is completed.

Read-related commands (Read, Fast Read, Read Status Register or Release from Deep Power-Down, Read Device ID) shifts out data from the device. CS# can be driven high after any bit of the output data sequence.

For other commands including Page Program, Sector Erase, Block Erase, Chip Erase, Write Status Register, Write Enable, Write Disable or Deep Power-Down, CS# must be driven high exactly at a byte boundary; otherwise if CS# is driven high at any time when the input byte is not a full byte, the command is ignored and WEL will not be reset.

Table 14: Command Definitions (Standard SPI, Dual SPI)

Command	Byte 1	Byte 2	Byte 3	Byte 4	Byte 5	Byte 6
Enable Reset	66h					
Reset	99h					
Read Unique ID	4Bh	dummy	dummy	dummy	dummy	UID63-UID0

Read Manufacturer / Device ID	90h	dummy	dummy	{7'h0,0/1b}	(M7-M0)	ID7-ID0
Read Manufacturer / Device ID by Dual I/O	92h	A23-A8	A7-A0, M7-M0	(M7-M0) (ID7-ID0)		
Read Identification	9Fh	M7-M0	ID15-ID8	ID7-ID0		
Write Enable	06h					
Write Disable	04h					
Read Data	03h	A23-A16	A15-A8	A7-A0	D7-D0	
Fast Read	0Bh	A23-A16	A15-A8	A7-A0	dummy	D7-D0
Dual Output Fast Read	3Bh	A23-A16	A15-A8	A7-A0	dummy	D7-D0
Dual I/O Fast Read	BBh	A23-A8	A7-A0, M7-M0	D7-D0		
Volatile SR Write Enable	50h					
Read Status Register-1	05h	S7-S0				
Read Status Register-2	35h	S15-S8				
Write Status Register-1	01h	S7-S0	(S15-S8)			
Write Status Register-2	31h	S15-S8				
Erase Security Registers	44h	A23-A16	A15-A8	A7-A0		
Program Security Registers	42h	A23-A16	A15-A8	A7-A0	D7-D0	D7-D0
Read Security Registers	48h	A23-A16	A15-A8	A7-A0	dummy	D7-D0
Read Serial Flash Discoverable Parameter	5Ah	A23-A16	A15-A8	A7-A0	dummy	D7-D0
Sector Erase(0.5K)	8Ah	A23-A16	A15-A8	A7-A0		
Sector Erase(4KB)	20h	A23-A16	A15-A8	A7-A0		
Block Erase (32KB)	52h	A23-A16	A15-A8	A7-A0		
Block Erase (64KB)	D8h	A23-A16	A15-A8	A7-A0		
Chip Erase	C7h/ 60h					
Page Program	02h	A23-A16	A15-A8	A7-A0	D7-D0	
Dual Input Page Program	A2h	A23-A16	A15-A8	A7-A0	D7-D0	
Release From Deep Power-Down /Device ID	ABh	dummy	dummy	dummy	(ID7-ID0)	
Release From Deep Power-Down	ABh					
Deep Power-Down	B9h					
Continuous Read Mode Reset	FFh					

Note:

(1) The 01h command could continuously write up to two Bytes to registers SR1, SR2.

8.1. Write Enable (WREN) (06h)

The Write Enable instruction sets the Write Enable Latch (WEL) bit in the Status Register to a 1. The WEL bit must be set prior to every Page Program, 0.5K Sector Erase(SE05K), Sector Erase, Block Erase, Chip

Erase and Write Status Register instruction. The Write Enable instruction is entered by driving CS# low, shifting the instruction code "06h" into the Data Input (DI) pin on the rising edge of CLK, and then driving CS# high.

Command sequence:

CS# goes low --> Send 06h command into SI pin --> CS# goes high.

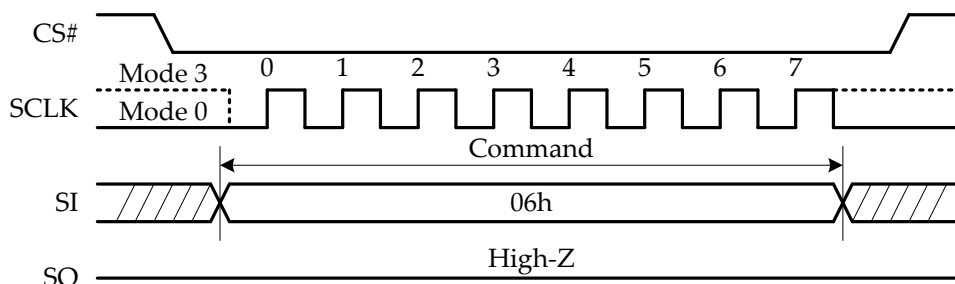


Figure 3: Write Enable (WREN) (06h) Command Sequence

8.2. Write Disable (WRDI) (04h)

The Write Disable instruction (Figure 4) resets the Write Enable Latch (WEL) bit in the Status Register to a 0. The Write Disable instruction is entered by driving CS# low, shifting the instruction code "04h" into the DI pin and then driving CS# high. Note that the WEL bit is automatically reset after Power-up and upon completion of the Write Status Register, Page Program, 0.5K Sector Erase(SE05K), Sector Erase, Block Erase and Chip Erase instructions.

Command Sequence:

Drive CS# low --> Send 04h command into SI pin --> Drive CS# high.

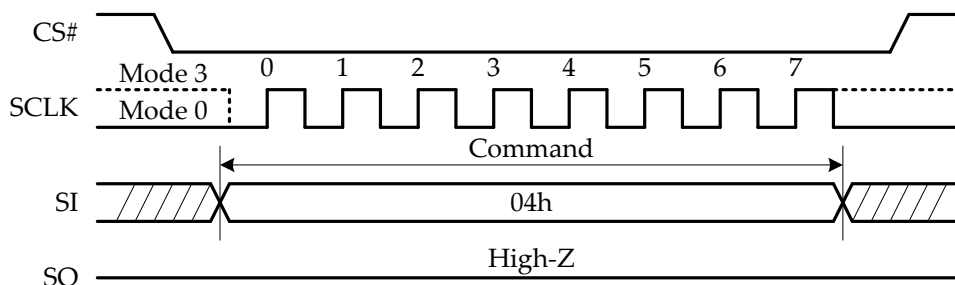


Figure 4: Write Disable (WRDI) (04h) Command Sequence

8.3. Write Enable for Volatile Status Register (50h)

The nonvolatile bits in the Status Register can also be written as volatile bits. This enables the host to quickly change the Status Register bits without the lengthy write cycle of nonvolatile bits, and it does not affect the endurance of the nonvolatile bits in the Status Register.

The 50h command does not set the WEL bit. It must be issued prior to WRSR command (01h, 31h); there should be no other commands inserted between 50h and WRSR command.

Command sequence:

Drive CS# low --> Send 50h command into SI pin --> Drive CS# high.

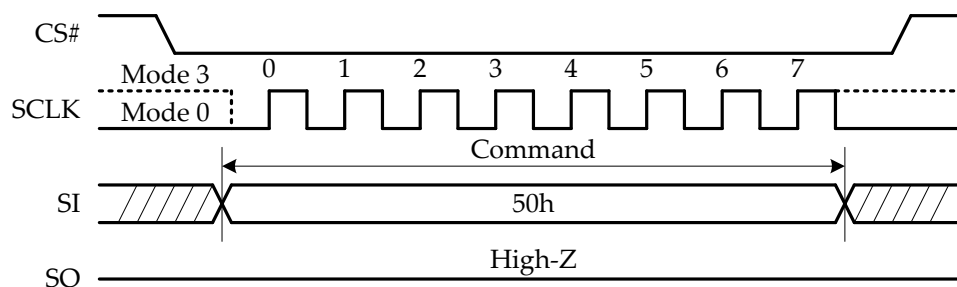


Figure 5: Write Enable for Volatile Status Register (50h) Command Sequence

8.4. Read Status Register (RDSR) (05h or 35h)

The RDSR commands enables the host to read out the Status Register. This command can be issued anytime, even while a WRSR, program or erase operation is in progress. It is recommended to use RDSR command to check the WIP bit before the next command is issued to the device.

The commands 05h, 35h reads SR1 (S7~S0), SR2 (S15~S8) , respectively. While CS# remains low, an RDSR command can output the designated Status Register continuously.

Command sequence:

Drive CS# low --> Send RDSR command into SI pin --> Receive output data on SO pin --> Drive CS# high.

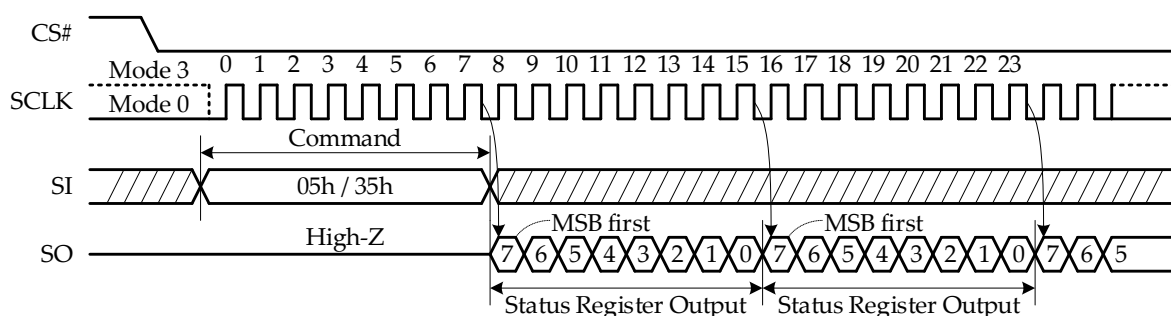


Figure 6: Read Status Register (RDSR) (05h or 35h) Command Sequence

8.5. Write Status Register (WRSR) (01h or 31h)

The WRSR command changes the values of Status Register. Before issuing WRSR command, a WREN command is needed to set the WEL bit.

The commands 01h, 31h writes SR1 (S7~S0), SR2 (S15~S8), respectively. And command 01h can also write SR1 (S7~S0) and SR2 (S15~S8) at the same time if CS# pull down 16 clocks.

Within the Status Register, read-only and reserved bits are not affected by WRSR command. Also, following the rules specified in Table.10, a combinations of SRP0 and SRP1 bit and WP# pin may protect the Status Register against any write operations.

For the WRSR command to take effect, CS# must be deasserted exactly at a byte boundary, otherwise the command is ignored. After CS# is driven high, a duration of t_w is required before self-timed write cycle is complete. During t_w , the host may read the Status Register to check WIP bit. WIP is 1 if the device is busy in the write cycle; when the process completes and the device is ready to accept new commands, WIP and WEL are both reset to 0.

Command sequence:

Drive CS# low --> Send WRSR command into SI pin --> Send write data into SI pin --> Drive CS# high.

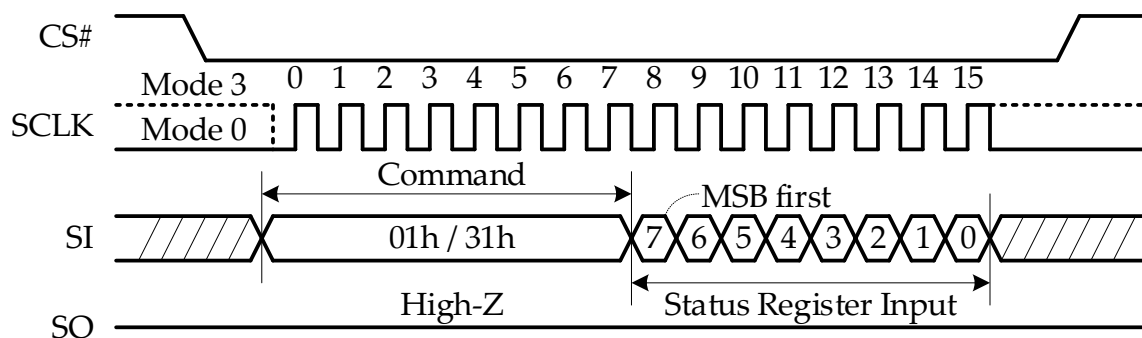


Figure 7: Write Status Register (WRSR) (01h or 31h) Command Sequence

8.6. Read Data Bytes (READ) (03h)

The READ command requires a 3-byte address (A23~A0) following the 03h command; the address can point to any location in the main memory array. Command and address are latched in on SCLK rising edge, and output data shifts out on SCLK falling edge. After each byte is shifted out, the address automatically increments to the next byte location; therefore, the entire memory can be output with a single READ command.

Maximum SCLK frequency of READ command is f_{r1} . The command is rejected if a WRSR, program or erase operation is in progress.

Command sequence:

Drive CS# low --> Send 03h command into SI pin --> Send 24-bit address into SI pin --> Receive output data on SO pin --> Drive CS# high.

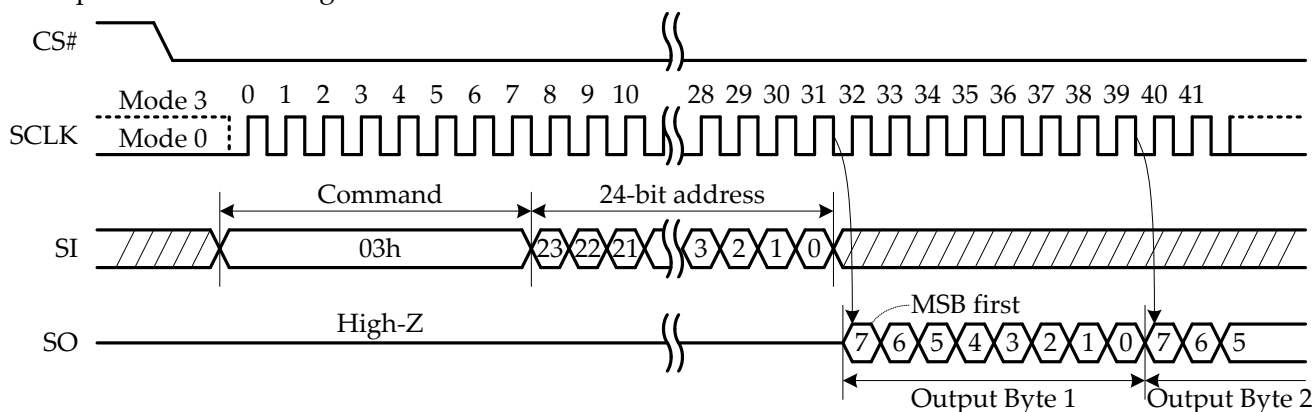


Figure 8: Read Data Bytes (READ) (03h) Command Sequence

8.7. Read Data Bytes at Higher Speed (Fast Read) (0Bh)

The Fast Read command has one more dummy byte after the 3-byte address compared with the READ command. Command and address are latched in on SCLK rising edge; output data shifts out on SCLK falling edge at a maximum clock frequency of f_{c3} .

Command sequence:

Drive CS# low --> Send 0Bh command into SI pin --> Send 24-bit address into SI pin --> 8 dummy SCLK cycles --> Receive output data on SO pin --> Drive CS# high.

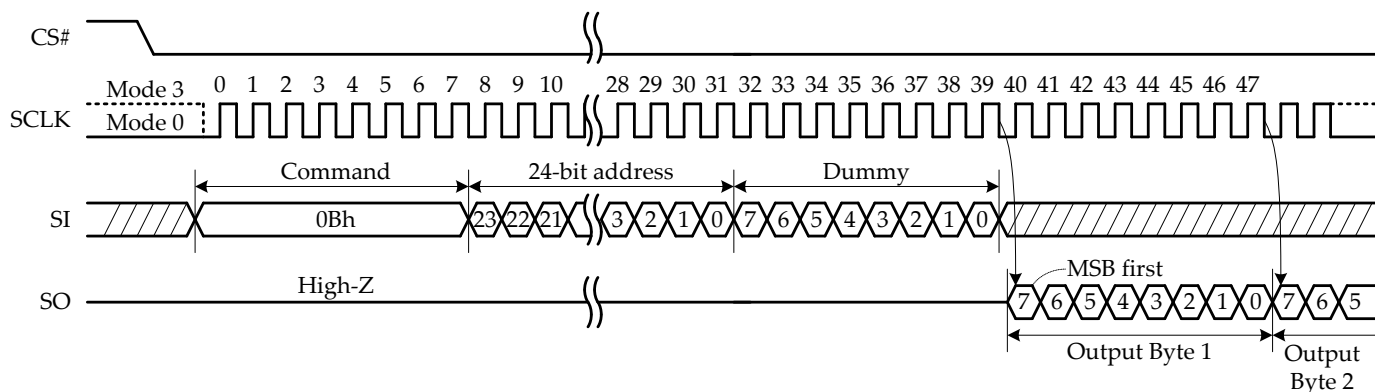


Figure 9: Read Data Bytes at Higher Speed (Fast Read) (0Bh) Command Sequence

8.8. Dual Output Fast Read (3Bh)

The 3Bh command is followed by 3-byte address and a dummy byte, and then two bits of data is shifted out per SCLK cycle on SI and SO pins. The address can point to any location in the main memory array, and it automatically increments to the next byte address after each byte of data is shifted out.

During the execution of 3Bh command, SI is a bidirectional IO which first acts as an input of command and address and then becomes an output for read data.

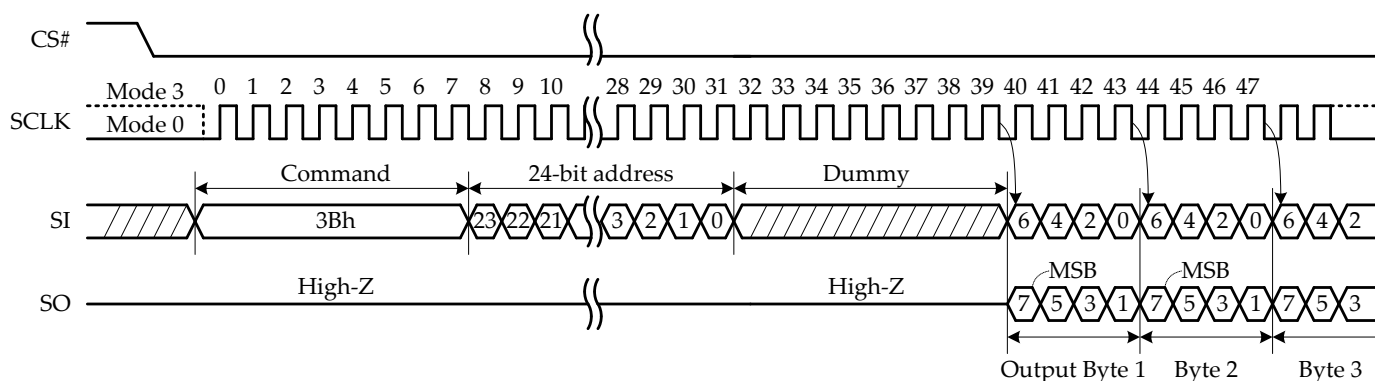


Figure 10: Dual Output Fast Read (3Bh) Command Sequence

8.9. Dual I/O Fast Read (BBh)

The BBh command is followed by 3-byte address and a "Continuous Read Mode" byte. Two dummy clocks are inserted. Address bytes and Mode bytes are latched in 2 bits per SCLK cycle on SI and SO pins, and then the memory content is shifted out 2 bits per clock cycle on the falling edge of SCLK. The first byte addressed can be at any location. The address automatically increments to the next byte after each byte is shifted out.

The "Continuous Read Mode" bits can further reduce command overhead. If (M7, M5) are (1, 1), then the command word BBh is not required for the next Dual I/O Fast Read command; otherwise, the device returns to normal operation mode and requires explicit command word for the next instruction. A Software Reset command (66h+99h) can reset (M5, M4) and bring the device back to normal operation.

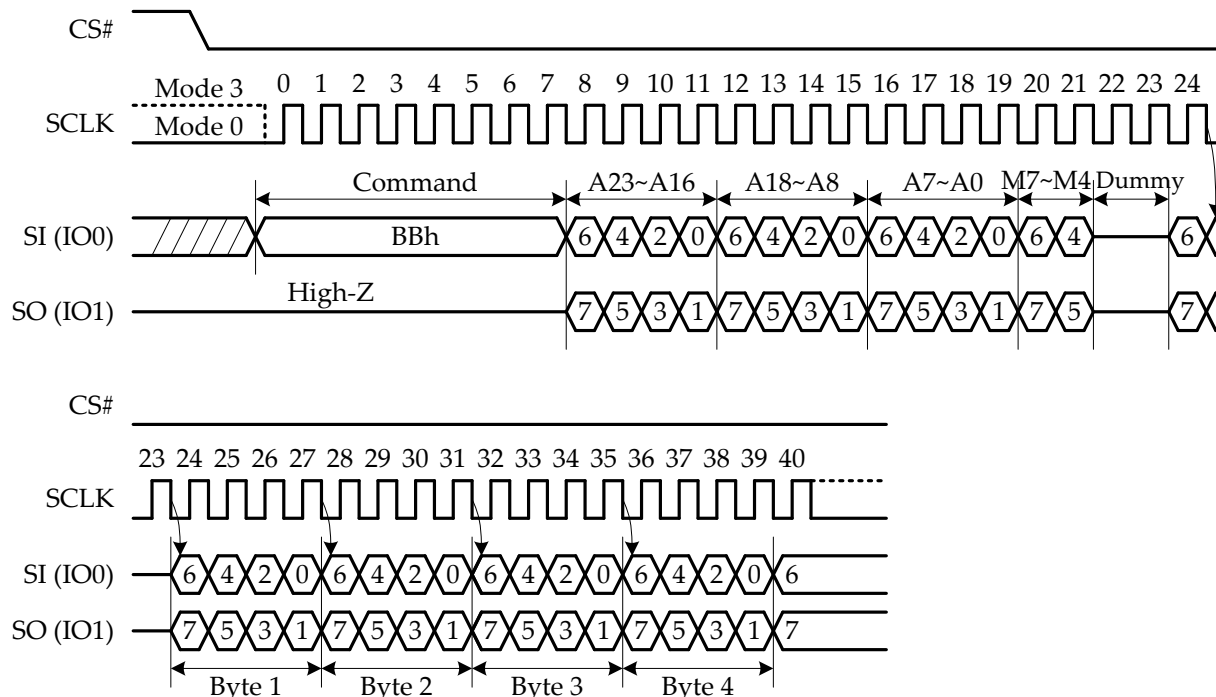


Figure 11: Dual I/O Fast Read (BBh) Command Sequence

8.9.1. Continuous Read Mode

If a previous BBh command has already set (M7, M5) to (1, 1), then the next Dual I/O Fast Read operation does not need the BBh opcode.

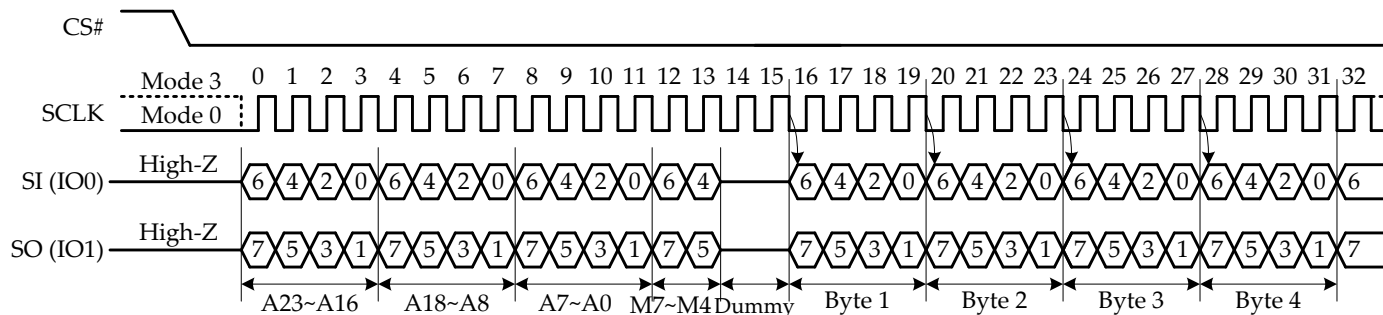


Figure 12: Dual I/O Fast Read (BBh) Command Sequence

8.10. Page Program (PP) (02h)

The PP command programs data to a specified location in the main memory array. The maximum amount of data to program in one PP operation is 256 bytes. WEL bit must be set to enable the device for programming operation. Attempting to program a memory location that has previously been programmed but not erased may corrupt the data.

The command sequence is as follows:

Drive CS# low --> Send in 02h opcode --> Send in three address bytes --> Send in data --> Drive CS# high.

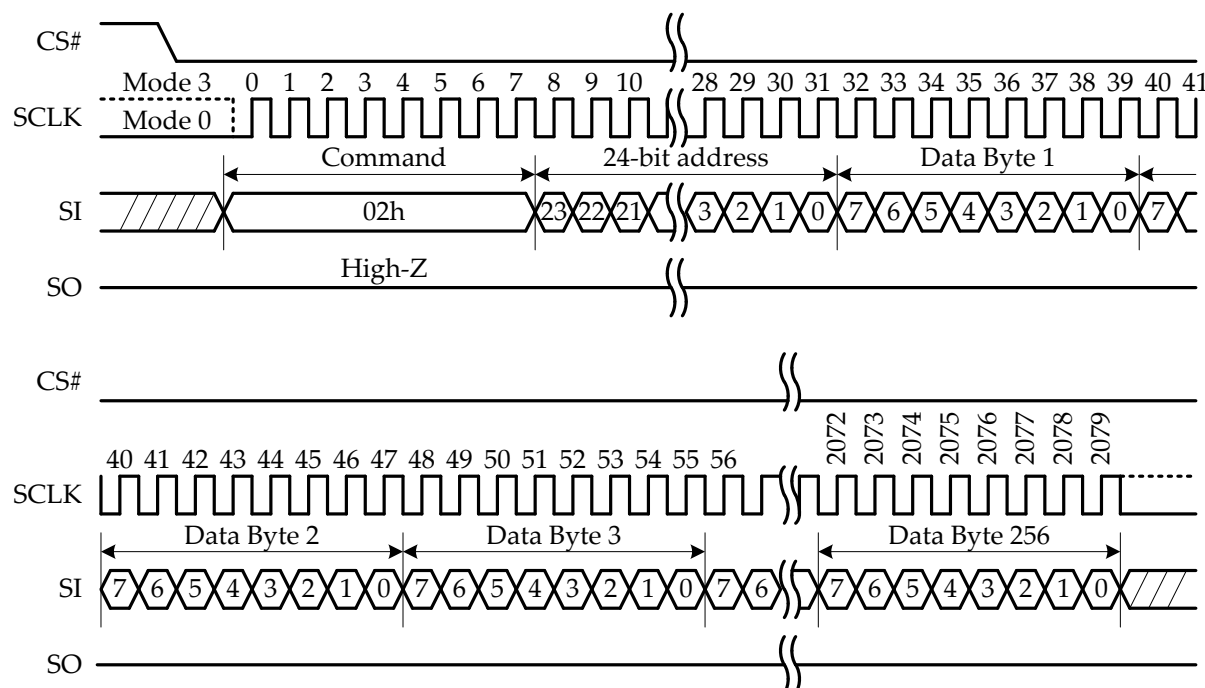


Figure 13: Page Program (PP) (02h) Command Sequence

The address specified in the 02h command is the starting address of the program operation; this address can point to any location in the main memory array. The host may send in an arbitrary amount of data, however when the address points to the ending boundary of the current page, it automatically rolls back to the starting boundary of that page. Thus, all data bytes of a PP command fall within a single 256-byte page in the main array.

If more than 256 bytes of data are sent to the device, only the last 256 bytes take effect, and all previously latched data are discarded. If less than 256 data bytes are sent, they can be correctly programmed at the target addresses without affecting other bytes in the same page.

The CS# pin must be driven high exactly at a byte boundary, otherwise the command is ignored. After CS# is driven high, a self-timed Page Program cycle (t_{PP}) is initiated. While the Page Program cycle is in progress, it is recommended to continuously check the WIP bit in the Status Register. After the programming cycle is complete, the WEL bit is reset to 0.

A Page Program (PP) command applied to a page which is protected by Block Protect bits (BP4, BP3, BP2, BP1, and BP0) is not executed.

8.11. Dual Input Page Program (A2h)

The Dual Input Page Program command is for programming the memory using two pins: IO0, IO1. The A2h command programs data to a specified location in the main memory array. The maximum amount of data to program in one PP operation is 256 bytes. WEL bit must be set to enable the device for programming operation. Attempting to program a memory location that has previously been programmed but not erased may corrupt the data.

The command sequence is shown in Figure 14. If more than 256 Bytes are sent to the device, previously latched data are discarded and the last 256 data Bytes are guaranteed to be programmed correctly within the same page. If less than 256 data Bytes are sent to device, they are correctly programmed at the requested addresses without having any effects on the other Bytes of the same page. CS# must be driven high after the eighth bit of the last data Byte has been latched in; otherwise the Dual Input Page Program command is not executed.

The command sequence is as follows:

Drive CS# low --> Send in A2h opcode --> Send in three address bytes --> Send in data --> Drive CS# high.

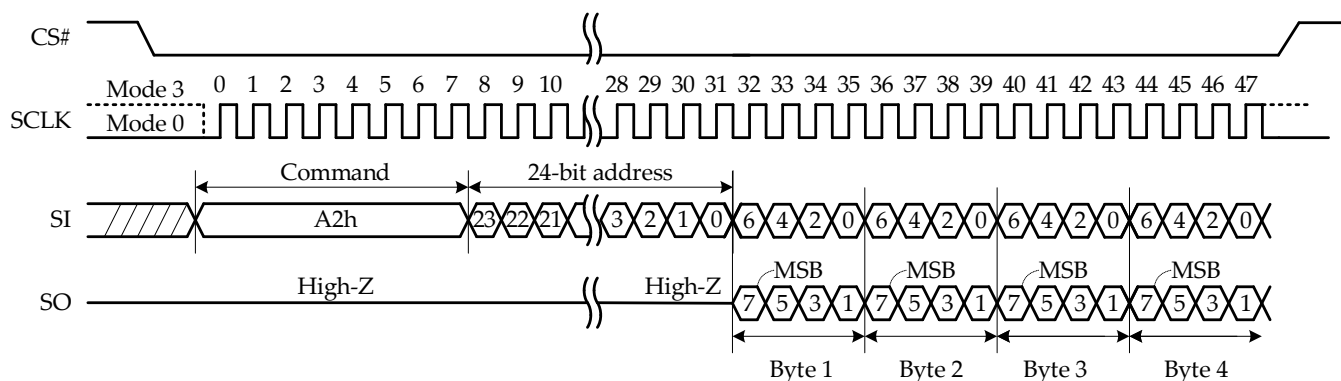


Figure 14: Dual Input Page Program (A2h) Command Sequence

8.12. 0.5KB Sector Erase (SE05K) (8Ah)

The Sector Erase 0.5K(SE05K) command is used to erase all the data of the chosen sector. A Write Enable (WREN) command must previously have been executed to set the Write Enable Latch (WEL) bit. The Sector Erase 0.5K (SE05K) command is entered by driving CS# low, followed by the command code, and 3-address Byte on DI. Any address inside the sector is a valid address for the Sector Erase 0.5K (SE05K) command. CS# must be driven low for the entire duration of the sequence.

The command sequence is as follows:

Drive CS# low --> Send in 8Ah opcode --> Send 3 bytes of address on SI --> Drive CS# high.

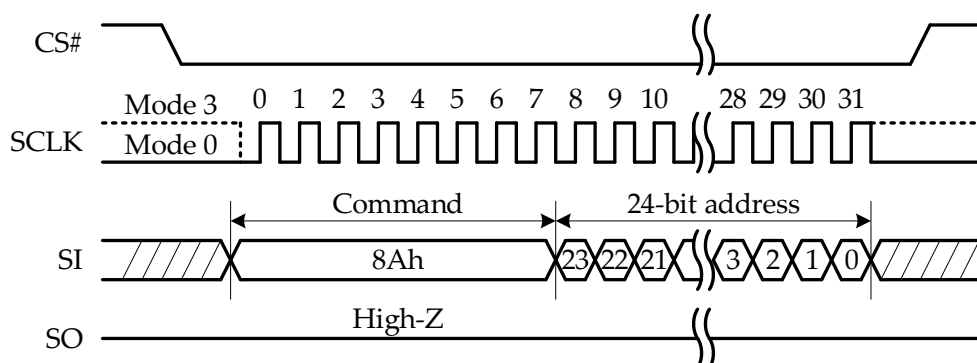


Figure 15: 0.5K Sector Erase Command Sequence

8.13. Sector Erase (SE) (20h)

SE command erases the specified 4KB sector and sets all bytes in the target sector to FFh. WREN command is required to set WEL bit prior to an erase operation. Any address within the sector is a valid address for the SE command.

The command sequence is as follows:

Drive CS# low --> Send in 20h opcode --> Send 3 bytes of address on SI --> Drive CS# high.

The CS# pin must be driven high after the eighth bit of the 3-byte address input, otherwise the erase operation is not executed. After CS# is driven high, the device internally initiates a self-timed Sector Erase cycle (t_{SE}). It is recommended to poll WIP bit continuously while an SE operation is in progress. WIP is 1 during the self-timed Sector Erase cycle, and becomes 0 when it is complete. At some unspecified time before the erase cycle is complete, the WEL bit is reset.

A Sector Erase command applied to a sector which is protected by Block Protect bits (BP4, BP3, BP2, BP1, BP0) is not executed.

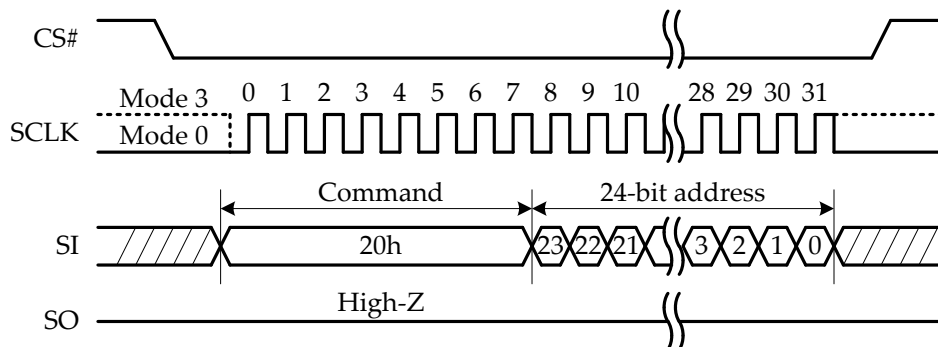


Figure 16: Sector Erase (SE) (20h) Command Sequence

8.14. 32KB Block Erase (BE) (52h)

32KB BE command erases the specified 32KB Block and sets all bytes in the target block to FFh. WREN command is required to set WEL bit prior to an erase operation. Any address within the 32KB block is a valid address for the BE command.

The command sequence is as follows:

Drive CS# low --> Send in 52h opcode --> Send 3 bytes of address on SI --> Drive CS# high.

The CS# pin must be driven high after the eighth bit of the 3-byte address input, otherwise the erase operation is not executed. After CS# is driven high, the device internally initiates a self-timed Block Erase cycle (t_{BE}). It is recommended to poll WIP bit continuously while a BE operation is in progress. WIP is 1 during the self-timed Block Erase cycle, and becomes 0 when it is complete. At some unspecified time before the erase cycle is complete, the WEL bit is reset.

A Block Erase command applied to a sector which is protected by Block Protect bits (BP4, BP3, BP2, BP1, BP0) is not executed.

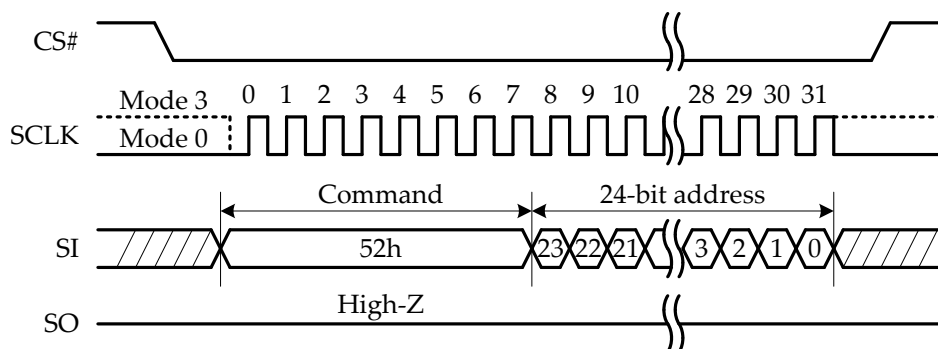


Figure 17: 32KB Block Erase (BE) (52h) Command Sequence

8.15. 64KB Block Erase (BE) (D8h)

64KB BE command erases the specified 64KB Block and sets all bytes in the target block to FFh. WREN command is required to set WEL bit prior to an erase operation. Any address within the 64KB block is a valid address for the BE command.

The command sequence is as follows:

Drive CS# low --> Send in D8h opcode --> Send 3 bytes of address on SI --> Drive CS# high.

The CS# pin must be driven high after the eighth bit of the 3-byte address input, otherwise the erase operation is not executed. After CS# is driven high, the device internally initiates a self-timed Block Erase cycle (t_{BE}). It is recommended to poll WIP bit continuously while a BE operation is in progress. WIP is 1 during the self-timed Block Erase cycle, and becomes 0 when it is complete. At some unspecified time before the erase cycle is complete, the WEL bit is reset.

A Block Erase command applied to a sector which is protected by Block Protect bits (BP4, BP3, BP2, BP1, BP0) is not executed.

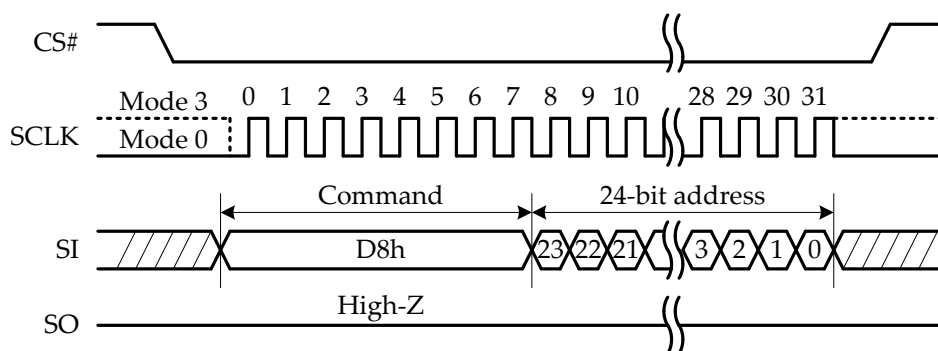


Figure 18: 64KB Block Erase (BE) (D8h) Command Sequence

8.16. Chip Erase (CE) (60h/C7h)

Chip Erase command erases the entire main memory array and sets all bytes in the array to FFh. WREN command is required to set WEL bit prior to an erase operation. The command sequence is as follows:
Drive CS# low --> Send in 60h or C7h opcode --> Drive CS# high.

The CS# pin must be driven high after the eighth bit of the command input, otherwise the erase operation is not executed. After CS# is driven high, the device internally initiates a self-timed Chip Erase cycle (t_{CE}). It is recommended to poll WIP bit continuously while a CE operation is in progress. WIP is 1 during the self-timed Chip Erase cycle, and becomes 0 when it is complete. At some unspecified time before the erase cycle is complete, the WEL bit is reset.

When a Chip Erase command is applied to a device, if any part of the main array is protected by Block Protect bits (BP4, BP3, BP2, BP1, BP0), then the command is not executed.

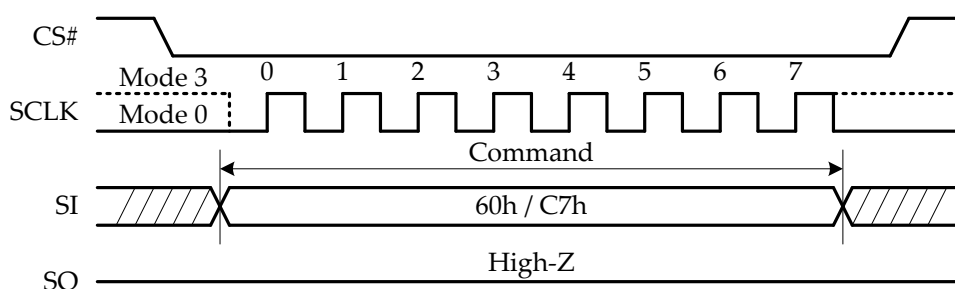


Figure 19: Chip Erase (CE) (60h/C7h) Command Sequence

8.17. Deep Power-Down (DP) (B9h)

DP command is the only way to bring the device into Deep Power-Down mode. In this mode, the supply current is reduced from standby current I_{CC1} to I_{CC2} . In this state, the device ignores all commands except "Release from Deep Power-Down and Read Device ID" (RDI) command. This command offers an extra software protection mechanism that protects the device from all WRSR, program or erase commands. The command sequence is as follows:

Drive CS# low --> Send in B9h opcode --> Drive CS# high.

The CS# pin must be driven high after the eighth bit of the command input, otherwise the operation is not executed. As soon as CS# is driven high, the device first returns to standby mode if no internal WRSR, program or erase operation is in progress. After a delay of t_{DP} , the device enters Deep Power-Down Mode.

and current consumption is greatly reduced.

RDI command and power-down can release the device from Deep Power-Down mode and bring it back to standby mode. A DP command while WRSR, program or erase operation is in progress that can be ignored.

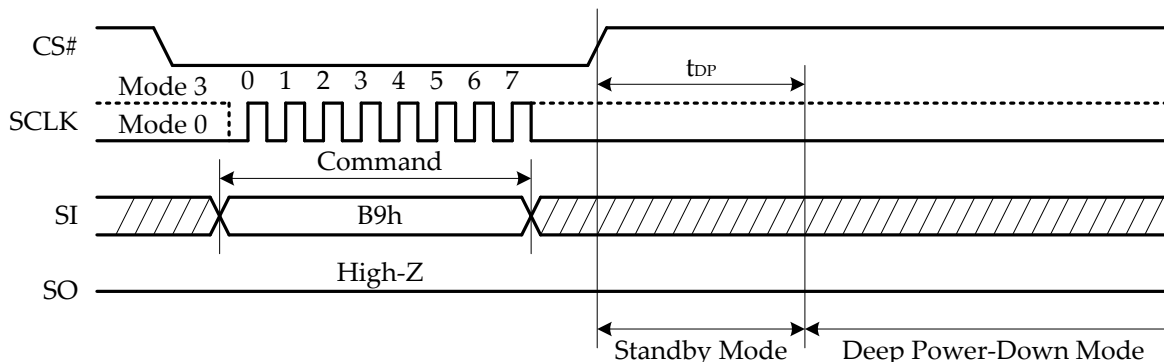


Figure 20: Deep Power-Down (DP) (B9h) Command Sequence

8.18. Read Unique ID (4Bh)

The Read Unique ID command accesses a factory-set read-only 128-bit number which is unique to each NM25WD40A device. The ID number can be used in conjunction with user software methods to help prevent illegal copying or cloning of a system. The command sequence is as follows:

Drive CS# pin low --> Shift in the 4Bh opcode --> Four bytes of dummy clocks --> Shift out the 128-Bit ID. Data is shifted out on the falling edge of SCLK.

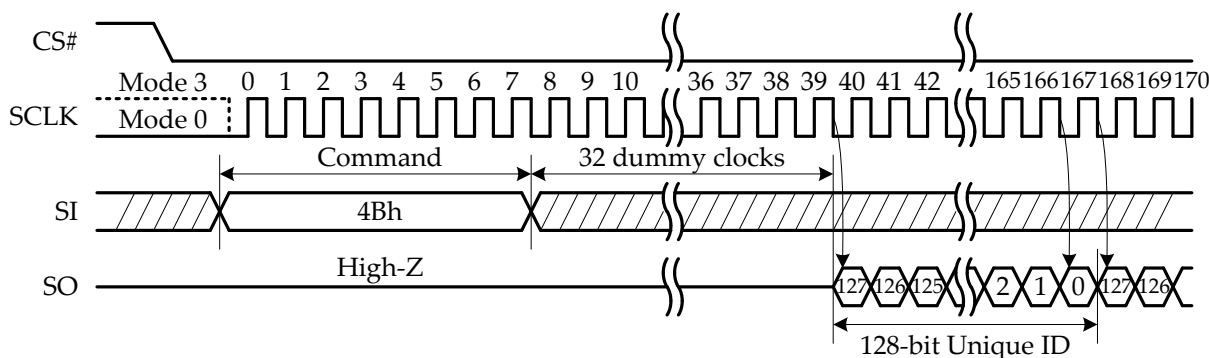


Figure 21: Read Unique ID (4Bh) Command Sequence

8.19. Release from Deep Power-Down and Read Device ID (RDI) (ABh)

When issued alone and without any dummy cycles, the ABh command releases the device from Deep Power-Down state or High Performance Mode.

If the device is previously in Deep Power-Down mode, then after CS# transitions high, it takes tRES1 before the device resumes normal operation and other commands are accepted. The CS# pin must remain high during tRES1; if the device is not previously in Deep Power-Down mode, then the transition to normal operation is immediate after CS# is deasserted.

If the ABh command is issued while a WRSR, program or erase operation is in progress, then the command is ignored

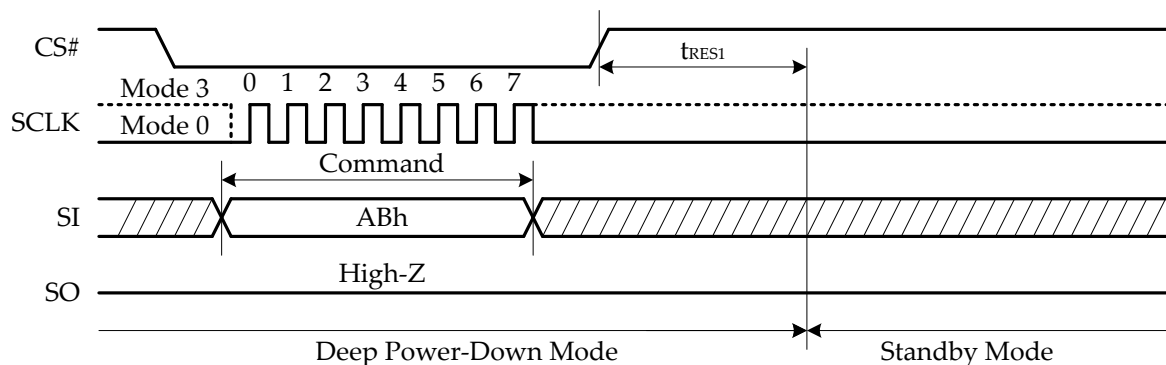


Figure 22: Release Power-Down (ABh) Command Sequence

If the device is previously in deep power-down mode, ABh can release the device from Deep Power-Down mode and obtain Device ID. The opcode is followed by three dummy bytes and the Device ID output byte. After CS# transitions high, it must remain high for at least tRES2 before the device returns to normal operation and other commands can be accepted.

If the ABh command is issued while a WRSR, program or erase operation is in progress, then the command is ignored.

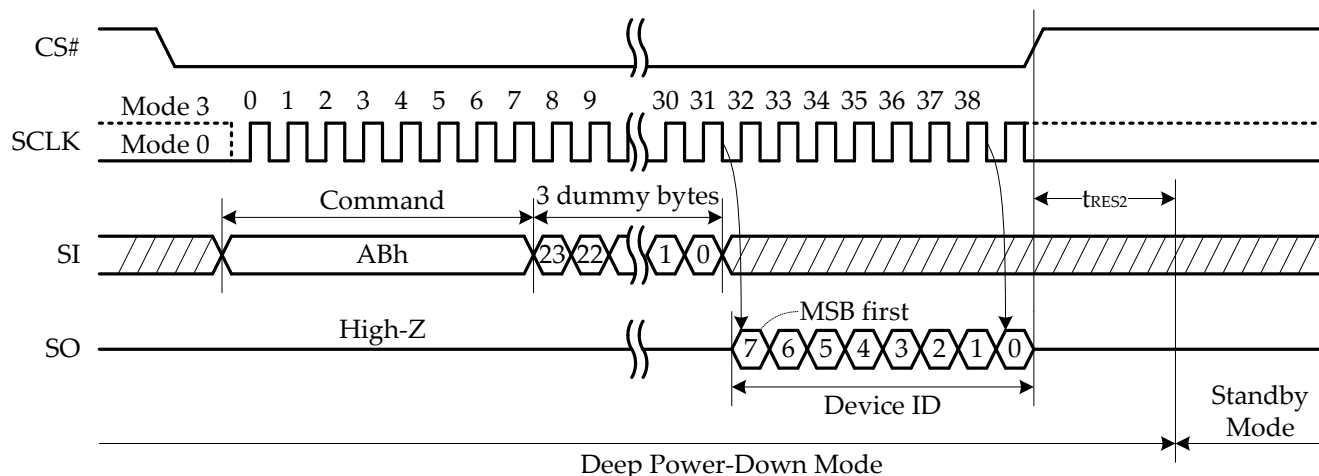


Figure 23: Release Power-Down and Read Device ID (ABh) Command Sequence

8.20. Read Manufacture ID / Device ID (REMS) (90h)

The 90h command provides both JEDEC assigned Manufacturer ID and Device ID. A 24-bit address is required following the 90h opcode. If address bit A0 is 0, then Manufacture ID is read out first; otherwise if A0 is 1, then Device ID is output first.

The command sequence is:

Drive CS# pin low --> Shift in 90h opcode --> Three bytes of address --> Shift out IDs.

Data is shifted out on SCLK falling edge. As long as CS# is low, the two IDs are repetitively output in turns.

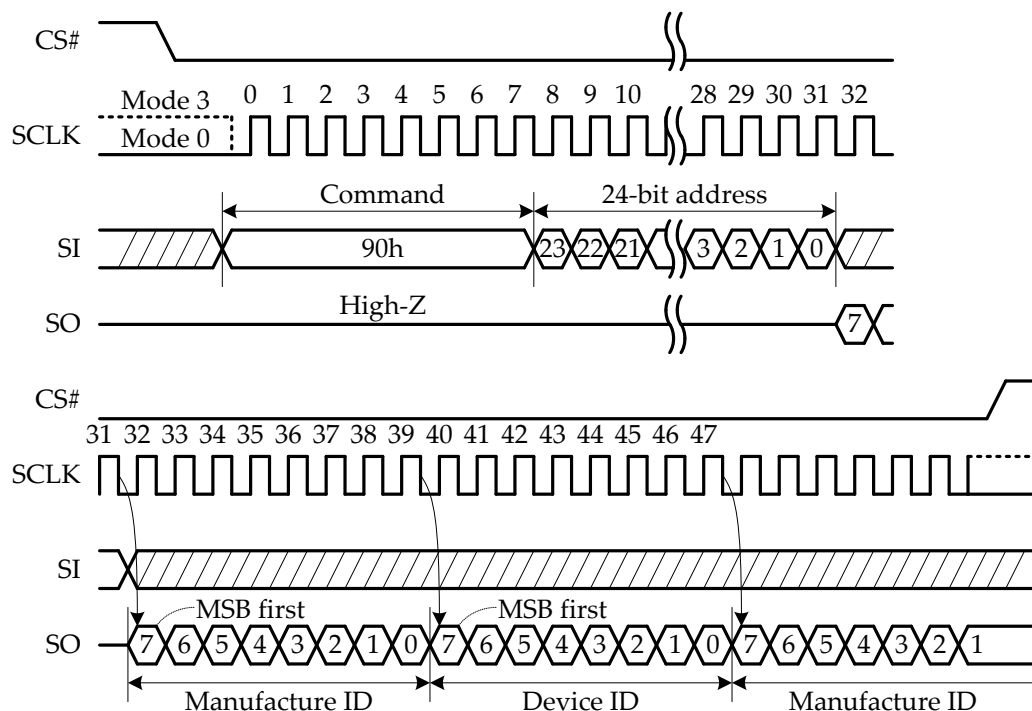


Figure 24: Read Manufacturer ID / Device ID (REMS) (90h) Command Sequence

8.21. Dual I/O Read Manufacturer ID / Device ID (92h)

The 92h command outputs Manufacturer ID and Device ID. A 24-bit address and 8 mode bits are required following the 92h opcode. If address bit A0 is 0, then Manufacturer ID is output first; otherwise if A0 is 1, then Device ID is output first. The mode bits in 92h command do not bring the device into continuous read mode.

The command sequence is:

Drive CS# pin low --> Shift in 92h opcode --> Three bytes of Address and one byte of Mode bits on IO0 and IO1 --> Shift out ID data on IO0 and IO1.

Data is shifted out on SCLK falling edge. As long as CS# is low, the two IDs are repetitively output in turns.

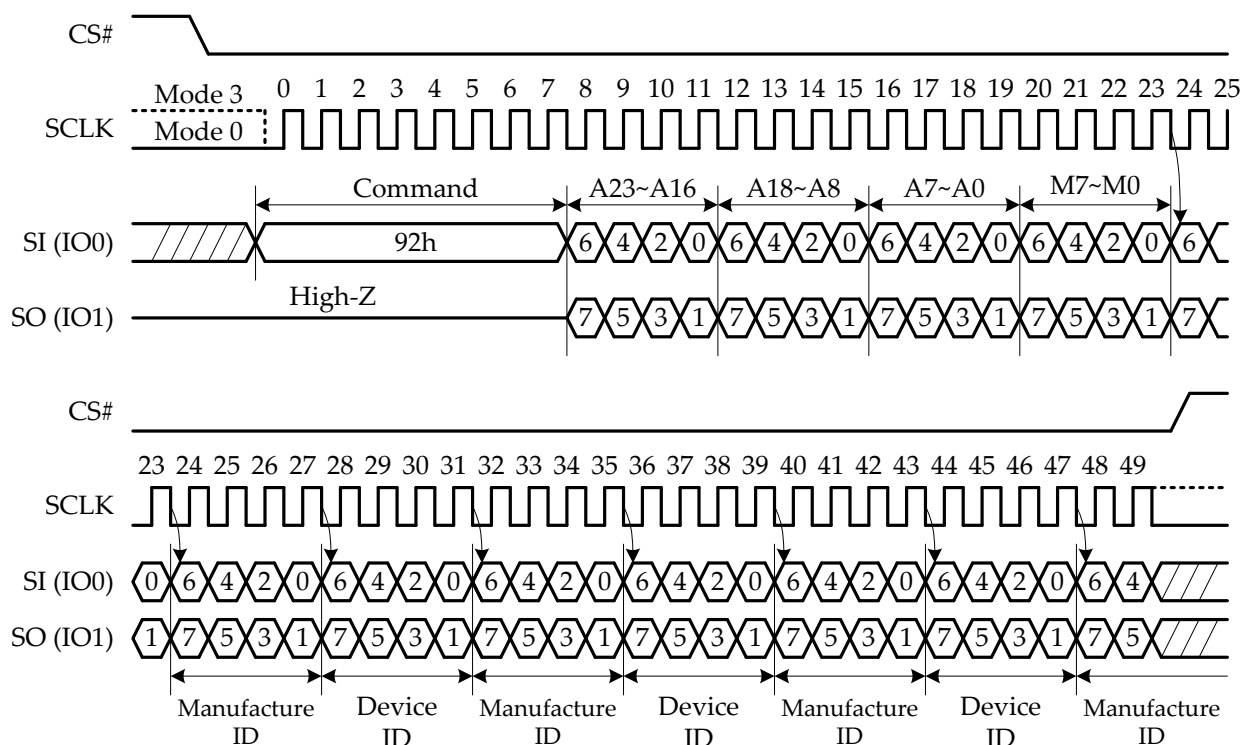


Figure 25: Dual I/O Read Manufacture ID / Device ID (92h) Command Sequence

8.22. Read Identification (RDID) (9Fh)

The 9Fh command outputs Manufacture ID, Memory Type and Memory Capacity ID codes. An RDID command during WRSR, program or erase cycle is ignored.

The command sequence is:

Drive CS# pin low --> Shift in 9Fh opcode --> Shift out Manufacture ID data byte --> Shift out memory type data byte --> Shift out memory capacity data byte.

Data is shifted out on SCLK falling edge. The host may terminate the command by driving CS# high at any time during data output. As long as CS# keeps low, the three IDs will be repetitively output in turns.

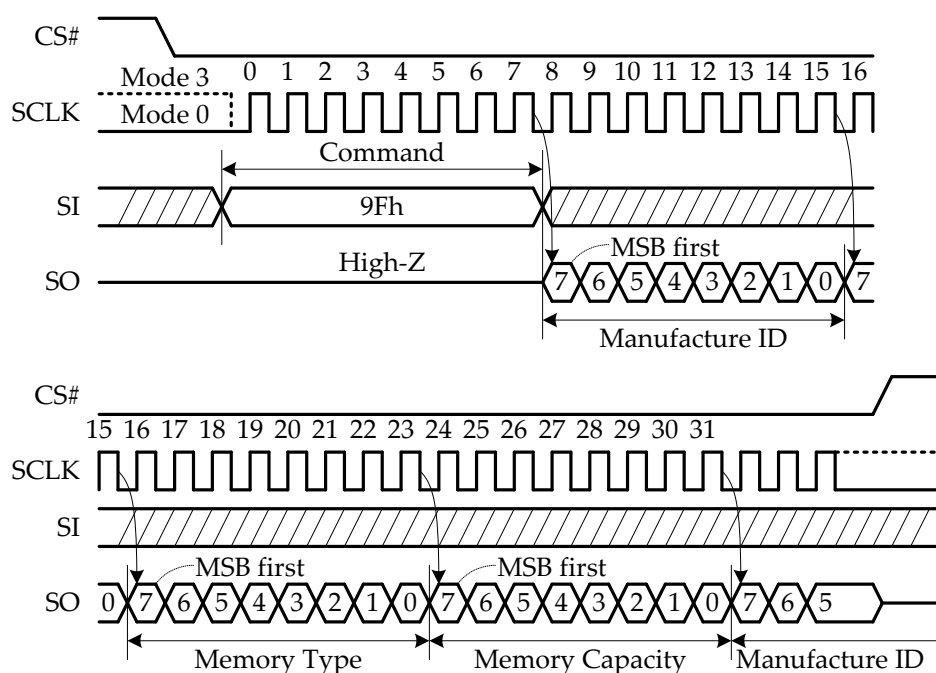


Figure 26: Read Identification (RDID) (9Fh) Command Sequence

8.23. Erase Security Registers (44h)

The three 512-byte Security Registers of the NM25WD40A device can be read, programmed or erased individually. The host may use Security Registers to store security or other important information separately from the main memory array.

Similar to Sector Erase and Block Erase commands, the 44h command requires that a WREN command be issued to set WEL bit = 1. The 44h command erases one of the three 512-bit Security Registers; the command sequence is as follows:

Drive CS# low --> Shift in 44h command --> Send 3-byte address on SI pin --> Drive CS# high.

The address definition of 44h command is specified in 5.3 *Security Register*. The CS# pin must be driven high after the last bit of address input, otherwise the command is ignored by the device.

After CS# transitions high, a self-timed Erase Security Registers cycle (t_{SE}) is initiated. The host may check the WIP bit while an erase cycle is in progress: the WIP bit is 1 during the self-timed Erase cycle, and is 0 when it is completed. At some unspecified time before the Erase cycle is completed, the WEL bit is reset.

Optionally, the Lock Bits (LB3, LB2, LB1) can each OTP protect a corresponding Security Register. Once protected, the Security Register is permanently protected against erase or program operations.

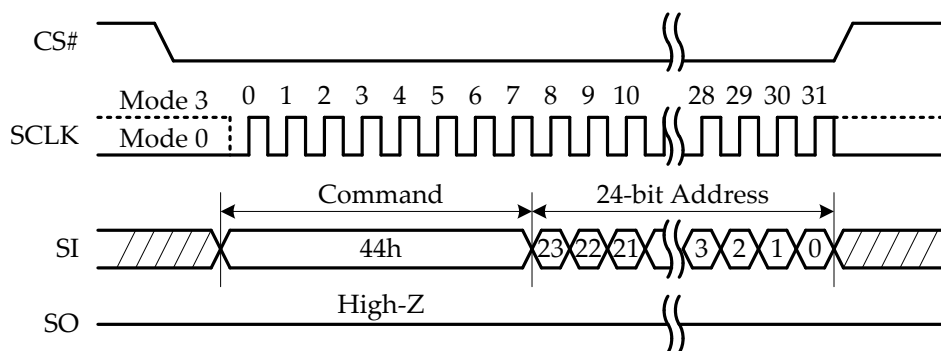


Figure 27: Erase Security Registers (44h) Command Sequence

8.24. Program Security Registers (42h)

The Program Security Register command programs data to a specified location in the Security Registers. WEL bit must be set to enable the device for programming operation. Attempting to program a memory location that has previously been programmed but not erased may corrupt the data.

The command sequence is as follows:

Drive CS# low --> Send in 42h opcode --> Send in 3-byte address -> Send in data -> Drive CS# high.

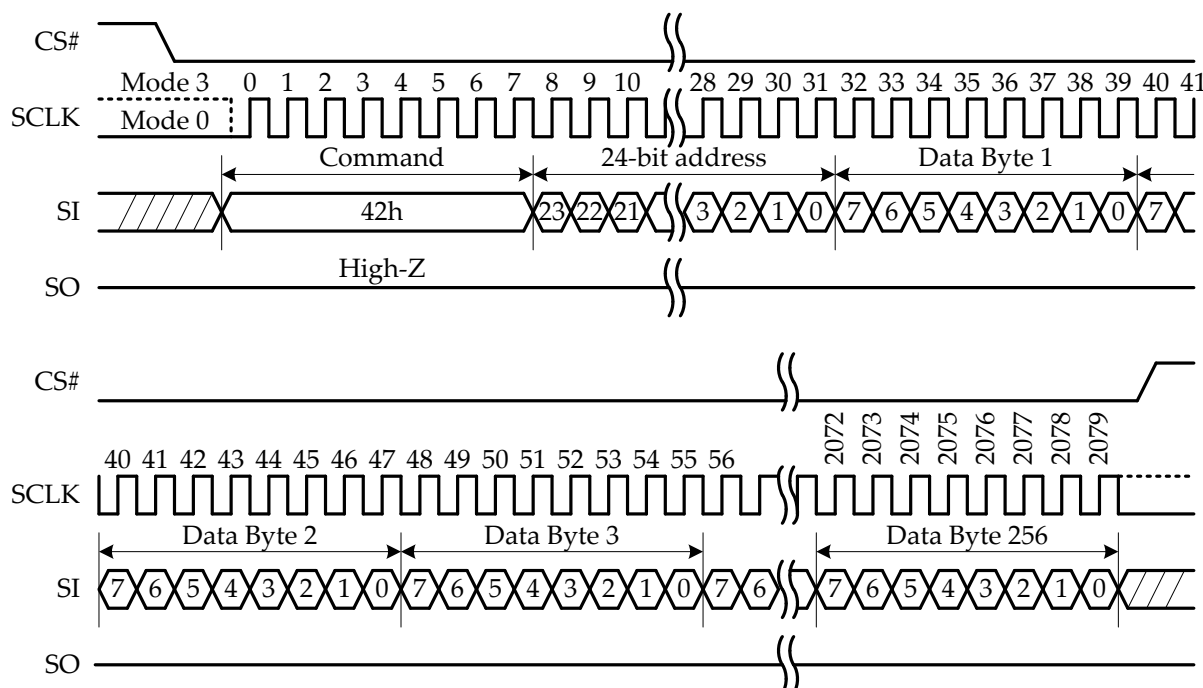


Figure 28: Program Security Registers (42h) Command Sequence

8.25. Read Security Registers (48h)

The Read Security Registers command is similar to Fast Read command. It outputs data bits at a maximum frequency of f_c . The first address can point to any location within a Security Register. The address automatically increments to the next byte address after each byte is shifted out. If the last byte address is reached, then the pointer will wrap back to the first byte address in the target Security Register.

The command sequence is as follows:

Drive CS# low --> Send in 48h opcode --> Send in 3-byte address --> One dummy byte --> Shift out read data on SO at SCLK falling edge.

The address definition of 48h command is specified in 5.3 Security Register.

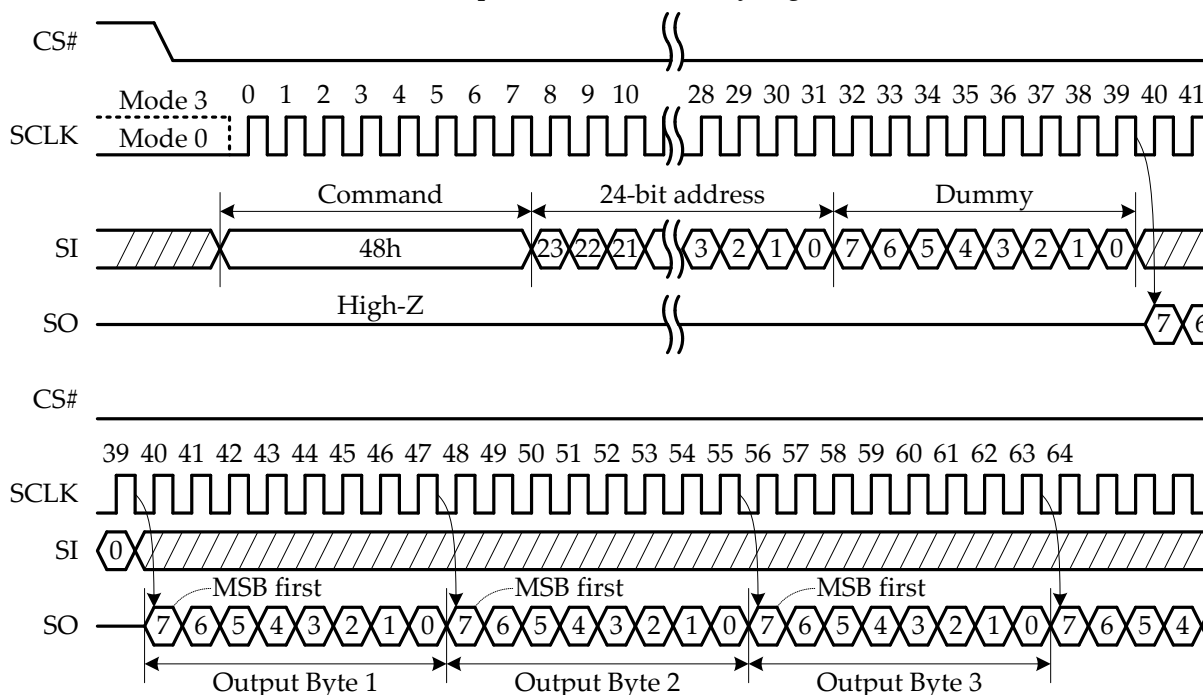


Figure 29: Read Security Registers (48h) Command Sequence

8.26. Enable Reset (66h) and Software Reset (99h)

The Software Reset command aborts all on-going internal operations, and brings the device back to its default power-on state. All volatile settings are lost, including Volatile Status Register bits, WEL, Continuous Read Mode bit setting (M7-M0). The command sequence is as follows.

The command sequence is as follows:

Drive CS# low --> Send in 66h opcode --> Drive CS# high --> Drive CS# low --> Send in 99h opcode --> Drive CS# high.

After CS# goes high, the software reset process takes t_{RST_R} , during which no command is accepted.

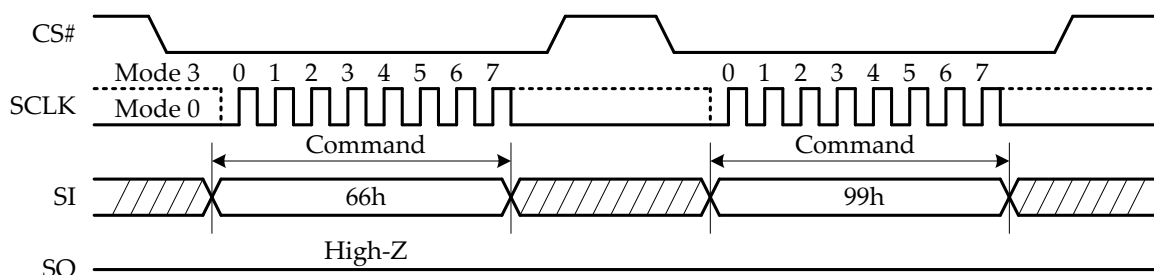


Figure 30: Enable Reset (66h) and Reset (99h) Command Sequence

8.27. Read Serial Flash Discoverable Parameter (5Ah)

The SFDP information is stored in a standard set of tables, which contain the functional and feature capabilities of the device. These tables can be interrogated by host to make adjustments needed to accommodate to different features from multiple vendors. SFDP is a JEDEC Standard (JESD216).

The address definition of 5Ah command is specified in 5.43 SFDP Register.

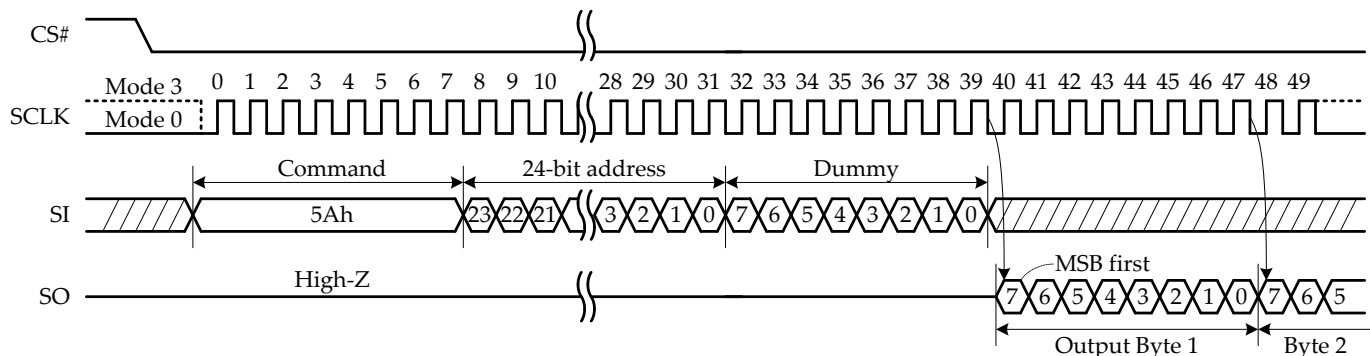


Figure 31: Read Serial Flash Discoverable Parameter (5Ah) Command Sequence

8.28. Continuous Read Mode Reset (CRMR) (FFH)

The Dual I/O Fast Read operations, “Continuous Read Mode” bits (M7-0) are implemented to further reduce command overhead. By setting the (M7-0) to AXH, the next Dual I/O Fast Read operations do not require the BBH command code.

Because NM25WD40A the has no hardware reset pin, so if Continuous Read Mode bits are set to “AXH”, the NM25WD40A will not recognize any standard SPI commands. So Continuous Read Mode Reset command will release the Continuous Read Mode from the “AXH” state and allow standard SPI command to be recognized. The command sequence is show in Figure 32.

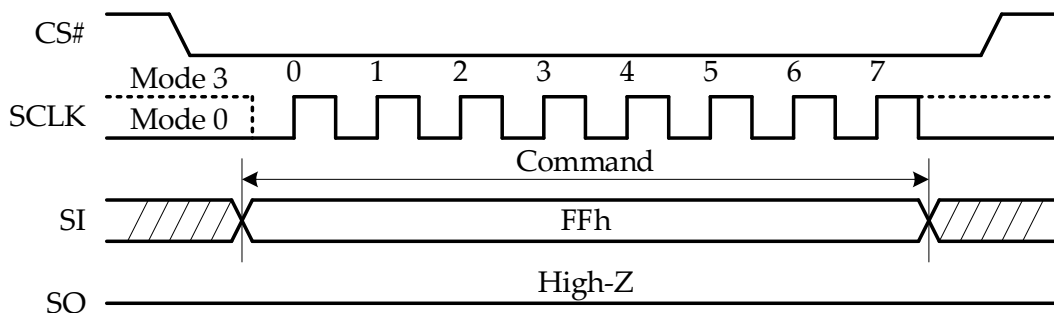


Figure 32: Continuous Read Mode Reset Command Sequence

9. Electrical Characteristics

9.1. Power-On Timing

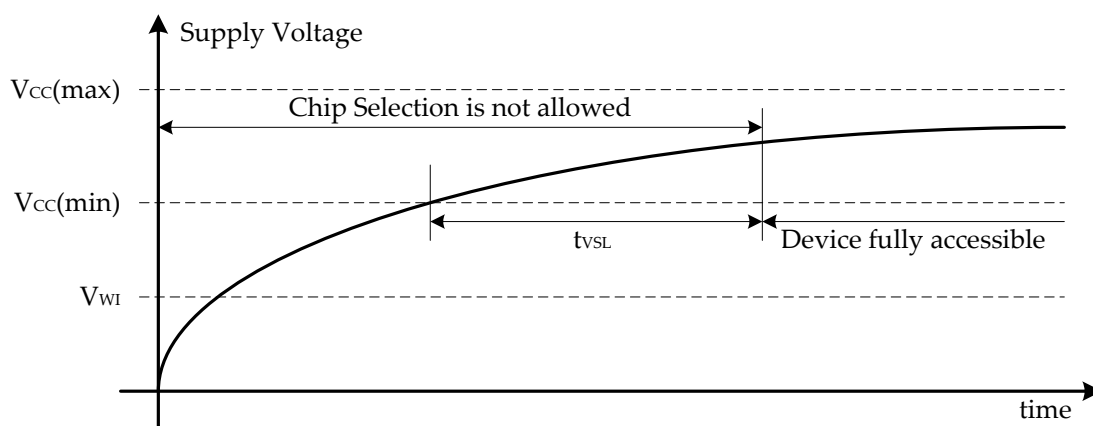


Figure 33: Power-On Timing Diagram

Table 15: Power-On Timing and Write Inhibit Threshold

Symbol	Comments	Min	Max	Unit
tvsl	V _{CC} (min) to earliest CS# Low	50	500	us
V _{WI}	Write Inhibit Voltage	1.45	1.55	V

9.2. Initial Delivery State

The device is delivered in the following status:

- (1) The main memory array is erased; all bits are set to 1 (all bytes are FFh);
- (2) The Status Register bits are all set to 0.

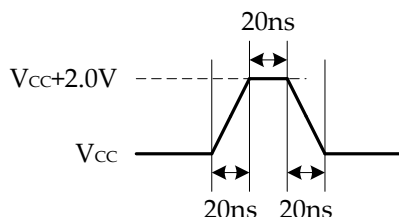
9.3. Absolute Maximum Ratings

Table 16: Absolute Maximum Ratings

Parameter	Value	Unit
Ambient Operating Temperature	-40 to 85	°C
Storage Temperature	-65 to 150	°C

Applied Input / Output Voltage	-0.6 to $V_{CC}+0.4$	V
Transient Input / Output Voltage (note: overshoot)	-2.0 to $V_{CC}+2.0$	V
V_{CC}	-0.6 to +4.2	V

Maximum Positive Overshoot Waveform



Maximum Negative Overshoot Waveform

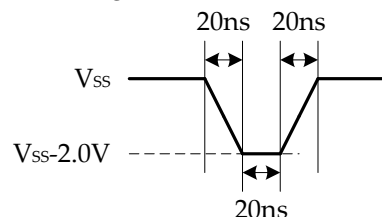


Figure 34: Maximum Positive / Negative Overshoot Timing Diagram

9.4. Recommended Operating Ranges

Table 17: Recommended Operating Ranges

Parameter	Symbol	Conditions	Spec		Unit
			Min	Max	
Supply Voltage	V_{CC}	FR=66MHz, fR=30MHz FR=104MHz, fR=50MHz	1.65 2.3	2.3 3.6	V
Ambient Temperature, Operating	T_A	Industrial	-40	105	$^{\circ}\text{C}$

9.5. DC Characteristics

Table 18: DC Characteristics at $T = -40^{\circ}\text{C} \sim 85^{\circ}\text{C}$, $V_{CC}=1.65 \sim 3.6V$

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
C_{IN}	Input Capacitance	$V_{IN}=0V$	----	----	6	pF
C_{OUT}	Output Capacitance	$V_{OUT}=0V$	----	----	8	pF
I_{LI}	Input Leakage Current	----	----	----	± 2	μA
I_{LO}	Output Leakage Current	----	----	----	± 2	μA
I_{CC1}	Standby Current	$CS\# = V_{CC}$, $V_{IN} = V_{CC}$ or V_{SS}	----	10	----	μA
I_{CC2}	Power-Down Current	$CS\# = V_{CC}$, $V_{IN} = V_{CC}$ or V_{SS}	----	0.65	22	μA
I_{CC3}	Current*1 I/O (Read)(0Bh) 80Mhz	$CLK = 0.1V_{CC} / 0.9V_{CC}$ $DO = \text{Open}$	----	2.8	4.4	mA
	Current*1 I/O (Read)(0Bh) 104Mhz	$CLK = 0.1V_{CC} / 0.9V_{CC}$ $DO = \text{Open}$	----	3.5	4.8	mA
I_{CC4}	Current Page Program	$CS\# = V_{CC}$	----	----	1.4	mA
I_{CC5}	Current Write Status Register	$CS\# = V_{CC}$	----	----	1.4	mA
I_{CC6}	Current Sector/Block Erase	$CS\# = V_{CC}$	----	----	1.3	mA
I_{CC7}	Current Chip Erase	$CS\# = V_{CC}$	----	----	1.3	mA

V _{IL}	Input Low Voltage	----	----	----	0.2V _{CC}	V
V _{IH}	Input High Voltage	----	0.7V _{CC}	----	----	V
V _{OL}	Output Low Voltage	I _{OL} =100μA	----	----	0.2	V
V _{OH}	Output High Voltage	I _{OH} =-100μA	V _{CC} -0.2	----	----	V

Table 19: DC Characteristics at T= -40°C~105°C, V_{CC}=1.65~3.6V

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
C _{IN}	Input Capacitance	V _{IN} =0V	----	----	6	pF
C _{OUT}	Output Capacitance	V _{OUT} =0V	----	----	8	pF
I _{LI}	Input Leakage Current	----	----	----	±2	μA
I _{LO}	Output Leakage Current	----	----	----	±2	μA
I _{CC1}	Standby Current	CS#=V _{CC} , V _{IN} =V _{CC} or V _{SS}	----	10	----	μA
I _{CC2}	Power-Down Current	CS#=V _{CC} , V _{IN} =V _{CC} or V _{SS}	----	0.65	25	μA
I _{CC3}	Current*1 I/O (Read)(0Bh) 80Mhz	CLK=0.1V _{CC} / 0.9V _{CC} DO=Open	----	2.8	4.4	mA
	Current*1 I/O (Read)(0Bh) 104Mhz	CLK=0.1V _{CC} / 0.9V _{CC} DO=Open	----	3.5	5	mA
I _{CC4}	Current Page Program	CS#=V _{CC}	----	----	1.5	mA
I _{CC5}	Current Write Status Register	CS#=V _{CC}	----	----	1.5	mA
I _{CC6}	Current Sector/Block Erase	CS#=V _{CC}	----	----	1.4	mA
I _{CC7}	Current Chip Erase	CS#=V _{CC}	----	----	1.4	mA
V _{IL}	Input Low Voltage	----	----	----	0.2V _{CC}	V
V _{IH}	Input High Voltage	----	0.7V _{CC}	----	----	V
V _{OL}	Output Low Voltage	I _{OL} =100μA	----	----	0.2	V
V _{OH}	Output High Voltage	I _{OH} =-100μA	V _{CC} -0.2	----	----	V

9.6. AC Characteristics

Table 20: AC Characteristics at T= -40°C~85°C, V_{CC}=1.65~3.6V, C_L=30pf

Symbol	Parameter	Min	Typ	Max	Unit
FR1	Clock frequency for BBh instructions, 2.7V-3.6V VCC	DC.	----	104	MHz
FR2	Clock frequency for BBh instructions, 2.3V-2.7V VCC	DC.	----	90	MHz
FR3	Clock frequency for BBh instructions, 1.65V-2.3V VCC	DC.	----	66	MHz
f _{R1}	Clock frequency for Read Data instruction (03h), 2.7V-3.6V VCC	DC.	----	50	MHz
f _{R2}	Clock frequency for Read Data instruction (03h), 1.65V-2.7V VCC	DC.	----	30	MHz
t _{CLH}	Serial Clock High Time	45% (1/fc)	----	----	ns
t _{CLL}	Serial Clock Low Time	45% (1/fc)	----	----	ns
t _{CLCH}	Serial Clock Rise Time (Slew Rate)	0.1	----	----	V/ns
t _{CHCL}	Serial Clock Fall Time (Slew Rate)	0.1	----	----	V/ns
t _{SLCH}	CS# Active Setup Time relative to CLK (1.65V-2.3V VCC)	10	----	----	ns

t _{SLCH}	CS# Active Setup Time relative to CLK (2.3V-3.6V VCC)	5	----	----	ns
t _{DVCH}	Data In Setup Time (1.65V-2.3V VCC)	3	----	----	ns
t _{DVCH}	Data In Setup Time (2.3V-3.6V VCC)	2	----	----	ns
t _{CHDX}	Data In Hold Time(1.65V-2.3V VCC)	3	----	----	ns
t _{CHDX}	Data In Hold Time (2.3V-3.6V VCC)	2	----	----	ns
t _{CHSH}	CS# Active Hold Time relative to CLK(1.65V-2.3V VCC)	10	----	----	ns
t _{CHSH}	CS# Active Hold Time relative to CLK (2.3V-3.6V VCC)	5	----	----	ns
t _{SHCH}	CS# Not Active Setup Time relative to CLK	5	----	----	ns
t _{SHSL}	CS# Deselect Time (Read / Write)	20	----	----	ns
t _{SHQZ}	Output Disable Time	----	----	6	ns
t _{CLQV}	Clock Low To Output Valid 1.65V-3.6V	----	----	7	ns
t _{CLQX}	Output Hold Time	1.2	----	----	ns
t _{WHSL}	Write Protect Setup Time Before CS# Low	20	----	----	ns
t _{SHWL}	Write Protect Hold Time After CS# High	100	----	----	ns
t _{D_P}	CS# High To Deep Power-Down Mode(1.65V-2.3V VCC)	----	----	31	μs
t _{D_P}	CS# High To Deep Power-Down Mode(2.3V-3.6V VCC)	----	----	25	μs
t _{RES1}	CS# High To Standby Mode With Electronic Signature Read(1.65V-2.3V VCC)	----	----	31	μs
t _{RES1}	CS# High To Standby Mode With Electronic Signature Read(2.3V-3.6V VCC)	----	----	25	μs
t _{RES2}	CS# High To Standby Mode Without Electronic Signature Read(1.65V-2.3V VCC)	----	----	31	μs
t _{RES2}	CS# High To Standby Mode Without Electronic Signature Read(2.3V-3.6V VCC)	----	----	25	μs
t _W	Write Status Register Cycle Time	----	5.2	8	ms
t _{BP1}	Byte program time (First Byte)	----	82	391	μs
t _{BP2}	Additional Byte program time (After First Byte)	----	5.3	8	μs
t _{PP}	Page Programming Time	----	0.8	4	ms
t _{SE}	Sector Erase Time(4K Bytes)	----	2.9	8	ms
t _{BE1}	Block Erase Time(32K Bytes)	----	2.9	8	ms
t _{BE2}	Block Erase Time(64K Bytes)	----	2.9	8	ms
t _{CE}	Chip Erase Time(NM25WD40A)	----	5.7	16	ms
t _{RST}	CS# High to next Instruction after Reset	----	----	150	μs

Notes:

1. Clock high + Clock low must be less than or equal to 1/fc..
2. Value guaranteed by design and/or characterization, not 100% tested in production..
3. Only applicable as a constraint for a Write Status Register instruction when Sector Protect Bit is set to 1.

Table 21: AC Characteristics at T= -40℃~105℃, V_{CC}=1.65~3.6V, C_L=30pf

Symbol	Parameter	Min	Typ	Max	Unit
F _{R1}	Clock frequency for BBh instructions, 2.7V-3.6V VCC	DC.	----	104	MHz

FR2	Clock frequency for BBh instructions, 2.3V-2.7V VCC	DC.	----	90	MHz
FR4	Clock frequency for BBh instructions, 1.65V-2.3V VCC	DC.	----	66	MHz
fr1	Clock frequency for Read Data instruction (03h), 2.7V-3.6V VCC	DC.	----	50	MHz
fr2	Clock frequency for Read Data instruction (03h), 1.65V-2.7V VCC	DC.	----	30	MHz
tCLH	Serial Clock High Time	45% (1/fC	----	----	ns
tCLL	Serial Clock Low Time	45% (1/fC	----	----	ns
tCLCH	Serial Clock Rise Time (Slew Rate)	0.1	----	----	V/ns
tCHCL	Serial Clock Fall Time (Slew Rate)	0.1	----	----	V/ns
tSLCH	CS# Active Setup Time relative to CLK (1.65V-2.3V VCC)	10	----	----	ns
tSLCH	CS# Active Setup Time relative to CLK (2.3V-3.6V VCC)	5	----	----	ns
tdVCH	Data In Setup Time (1.65V-2.3V VCC)	3	----	----	ns
tdVCH	Data In Setup Time (2.3V-3.6V VCC)	2	----	----	ns
tCHDX	Data In Hold Time (1.65V-2.3V VCC)	3	----	----	ns
tCHDX	Data In Hold Time (2.3V-3.6V VCC)	2	----	----	ns
tCHSH	CS# Active Hold Time relative to CLK(1.65V-2.3V VCC)	10	----	----	ns
tCHSH	CS# Active Hold Time relative to CLK (2.3V-3.6V VCC)	5	----	----	ns
tSHCH	CS# Not Active Setup Time relative to CLK	5	----	----	ns
tSHSL	CS# Deselect Time (Read / Write)	20	----	----	ns
tSHQZ	Output Disable Time	----	----	6	ns
tCLQV	Clock Low To Output Valid 1.65V-2.3V	----	----	7	ns
tCLQX	Output Hold Time	1.2	----	----	ns
tWHSL	Write Protect Setup Time Before CS# Low	20	----	----	ns
tSHWL	Write Protect Hold Time After CS# High	100	----	----	ns
tDP	CS# High To Deep Power-Down Mode(1.65V-2.3V VCC)	----	----	31	μs
tDP	CS# High To Deep Power-Down Mode(2.3V-3.6V VCC)	----	----	25	μs
tRES1	CS# High To Standby Mode With Electronic Signature Read(1.65V-2.3V VCC)	----	----	31	μs
tRES1	CS# High To Standby Mode With Electronic Signature Read(2.3V-3.6V VCC)	----	----	25	μs
tRES2	CS# High To Standby Mode Without Electronic Signature Read(1.65V-2.3V VCC)	----	----	31	μs
tRES2	CS# High To Standby Mode Without Electronic Signature Read(2.3V-3.6V VCC)	----	----	25	μs
tw	Write Status Register Time	----	5.2	8	ms
tBP1	Byte program time (First Byte)	----	82	391	μs
tBP2	Additional Byte program time (After First Byte)	----	5.3	8	μs
tPP	Page Program Time	----	0.8	4	ms
tSE	Sector Erase Time(4K Bytes)	----	2.9	8	ms

t_{BE1}	Block Erase Time(32K Bytes)	----	2.9	8	ms
t_{BE2}	Block Erase Time(64K Bytes)	----	2.9	8	ms
t_{CE}	Chip Erase Time(NM25WD40A)	----	5.7	16	ms
t_{RST}	CS# High to next Instruction after Reset	----	----	150	μ s

9.6.1. Serial Input Timing Diagram

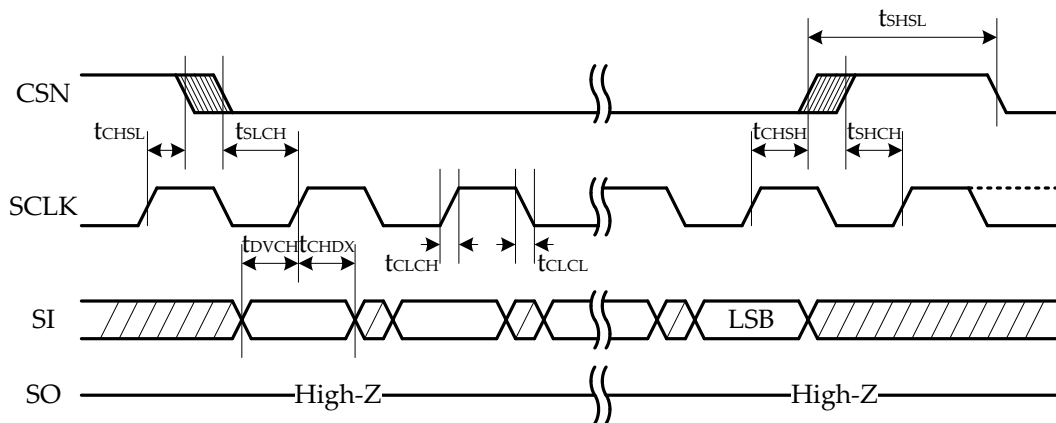


Figure 35: Serial Input Timing Diagram

9.6.2. Serial Output Timing Diagram

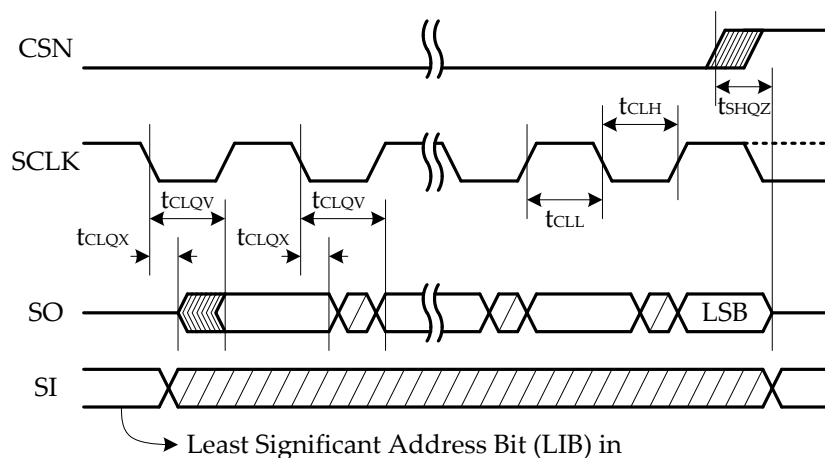


Figure 36: Serial Output Timing Diagram

9.6.3. Hold Timing Diagram

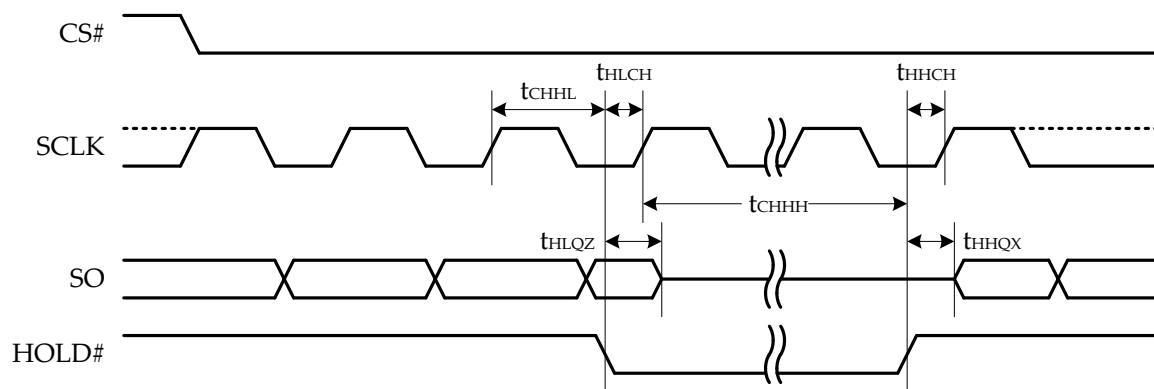


Figure 37: Hold Timing Diagram

9.7. Quality and Reliability Characteristics

Table 22: Quality and Reliability Characteristics

Symbol	Description	Min	Typ	Max	Units
T _{DR}	Data retention	----	20	----	Years
N _{PE}	Program/erase cycles (Endurance)	100,000	----	----	Cycles

10. Ordering Information

	NM	25	WD	40	A	X	X	X	X
Manufacturer									
NM: NEUMEM									
Product Family									
25: SPI NOR Flash									
29: Parallel NOR Flash									
Product Series									
D: 3.3V,4KB Uniform Sector, Dual mode									
LD: 1.8V,4KB Uniform Sector, Dual mode									
WD:1.8V-3.3V,4KB Uniform Sector, Dual mode									
Density									
05:512Kb									
10:1Mb									
20:2Mb									
40:4Mb									
80:8Mb									
16:16Mb									
32: 32Mbit									
64: 64Mbit									
128: 128Mbit									
256: 256Mbit									
512: 512Mbit									
01G: 1Gbit									
Product Version									
A: Version A									
B: Version B									
C: Version C									
Package Type									
B: FBGA-24									
D: DIP8 300mil									
F: FBGA-63									
O: SOP8 150mil									
P: SOP16 300mil									
Q: WSON8 (6*5mm)									
S: SOP8 208mil									
U: USON8 (2*3mm, 0.50mm thickness)									
W: Wafer									
Y: WSON8 (8*6mm)									
Z: TFBGA24 (6*4 Ball Array)									
Temperature Range									
C:Commercial (0°C to +70°C)									
I: Industrial (-40°C to +85°C)									
J: Industrial Plus (-40°C to +105°C)									
A: Automotive (-40°C to +125°C)									
Green Code									
G: Pb Free & Halogen Free Green Package									
Packing Type									
T or no mark: Tube									
Y: Tray									
R: Tape & Reel									

Figure 38: Device Ordering Information

11. Package Information

11.1. SOP8 (208mil)

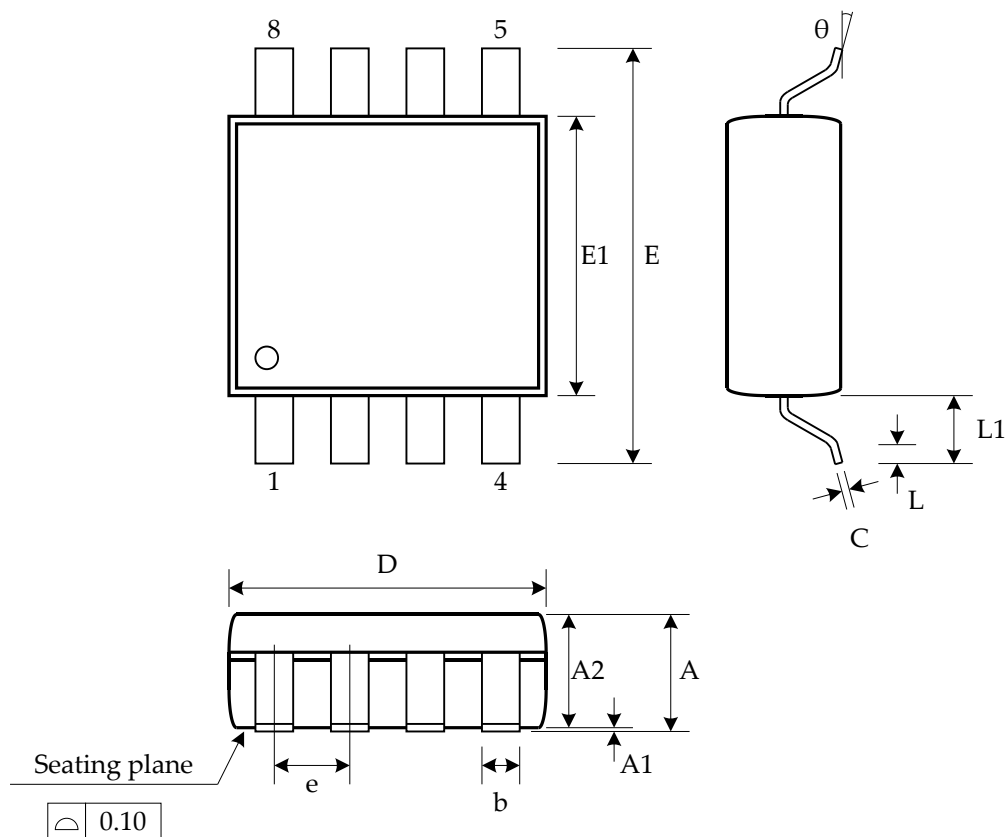


Figure 39: SOP8(208mil) Package

Table 23: The Package Dimensions of SOP8(208mil)

Symbol		A	A1	A2	b	C	D	E	E1	e	L	L1	θ
Unit													
mm	MIN.		0.05	1.25	0.31	0.15	4.80	5.80	3.80		0.40	1.20	0
	NOM.		0.15	1.40	0.41	0.20	4.90	6.00	3.90	1.27 BSC	-	1.31	
	MAX.	1.75	0.25	1.55	0.51	0.25	5.00	6.20	4.00		0.80	1.41	8
Inch	MIN.		0.002	0.049	0.012	0.006	0.189	0.228	0.150		0.016	0.048	
	NOM.		0.006	0.055	0.016	0.008	0.193	0.236	0.154	0.050 BSC		0.052	
	MAX.	0.069	0.010	0.061	0.020	0.010	0.197	0.244	0.157		0.031	0.056	

Notes:

1. Package length and width do not include mold flash.
2. Seating plane: Max. 0.10mm.

11.2. SOP8 (150mil)

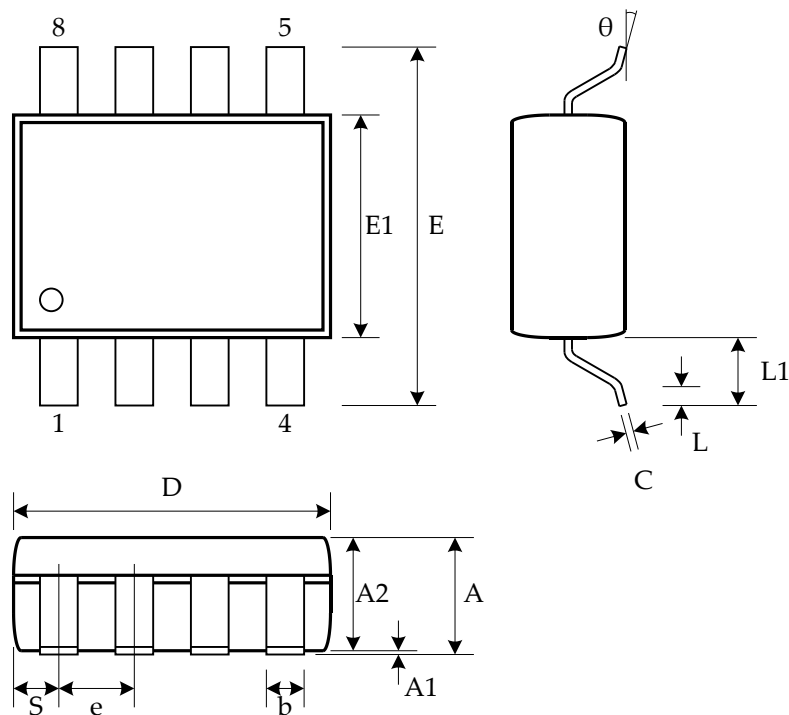


Figure 40: SOP8(150mil) Package

Table 24: The Package Dimensions of SOP8(150mil)

Symbol		A	A1	A2	b	C	D	E	E1	e	L	L1	S	θ
Unit														
mm	MIN.	--	0.10	1.35	0.36	0.15	4.77	5.80	3.80	--	0.46	0.85	0.41	0
	NOM.	--	0.15	1.45	0.41	0.20	4.90	5.99	3.90	1.27	0.66	1.05	0.54	5
	MAX.	1.75	0.20	1.55	0.51	0.25	5.03	6.20	4.00	--	0.86	1.25	0.67	8
Inch	MIN.	--	0.004	0.053	0.014	0.006	0.188	0.228	0.150	--	0.018	0.033	0.016	0
	NOM.	--	0.006	0.057	0.016	0.008	0.193	0.236	0.154	0.05	0.026	0.041	0.021	5
	MAX.	0.069	0.008	0.061	0.020	0.010	0.198	0.244	0.158	--	0.034	0.049	0.026	8

Notes:

Package length and width do not include mold flash.

11.3. TSSOP8 (173mil)

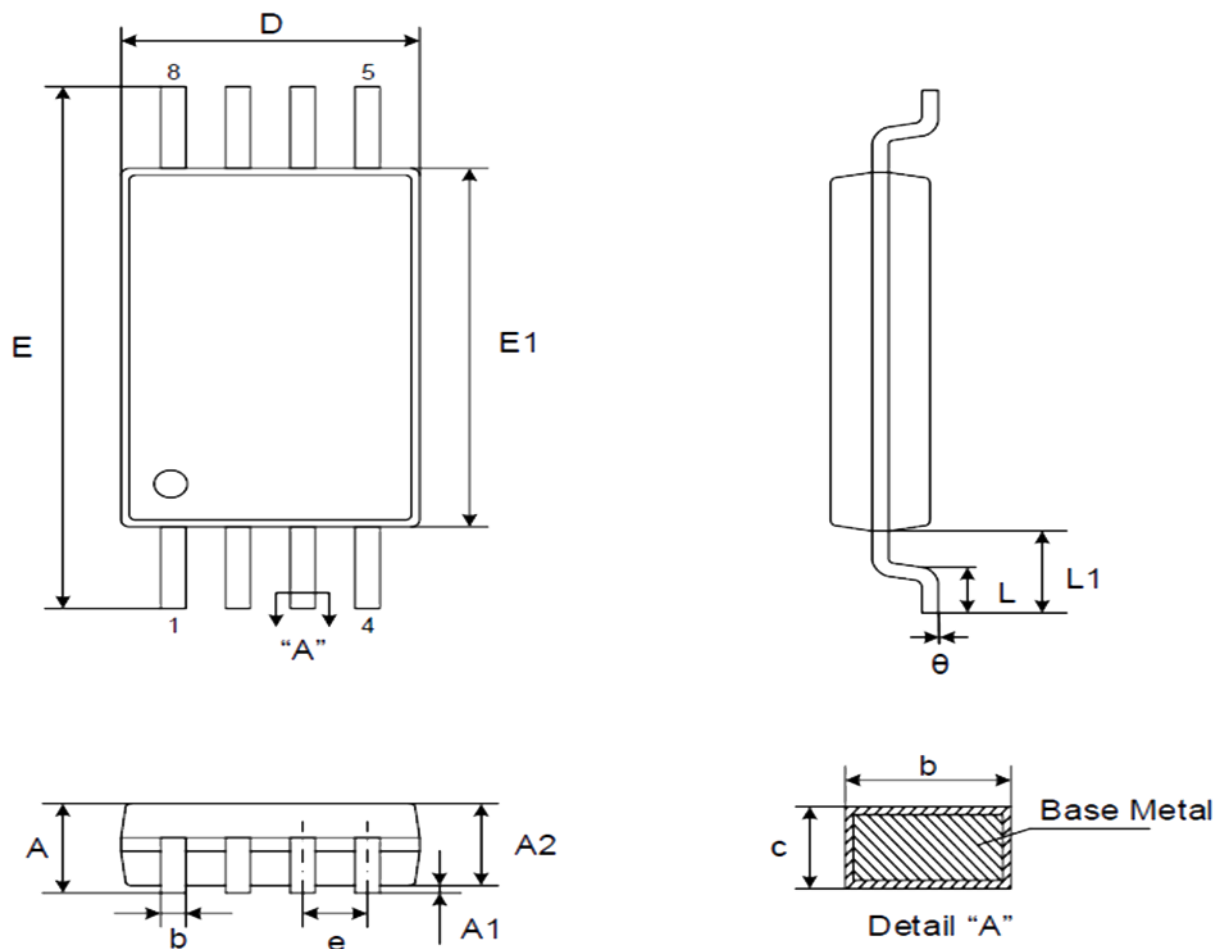


Figure 41: SOP8(150mil) Package

Table 25: The Package Dimensions of TSSOP8(173mil)

Symbol		A	A1	A2	b	c	D	E	E1	e	L	L1	θ
Unit													
mm	MIN.	-	0.05	0.80	0.20	0.10	2.90	6.30	4.30	0.65	0.85	0.45	0°
	NOM.	-	0.10	0.90	0.25	0.15	3.00	6.40	4.40		1.00	0.60	4°
	MAX.	1.20	0.15	1.00	0.30	0.20	3.10	6.50	4.50		1.15	0.75	8°
Inch	MIN.	-	0.002	0.031	0.008	0.004	0.114	0.248	0.169	0.026	0.033	0.018	0°
	NOM.	-	0.004	0.035	0.010	0.006	0.118	0.252	0.173		0.039	0.024	4°
	MAX.	0.047	0.006	0.039	0.012	0.008	0.122	0.256	0.177		0.045	0.030	8°

Notes:

Package length and width do not include mold flash.

11.4. DIP8 (300mil)

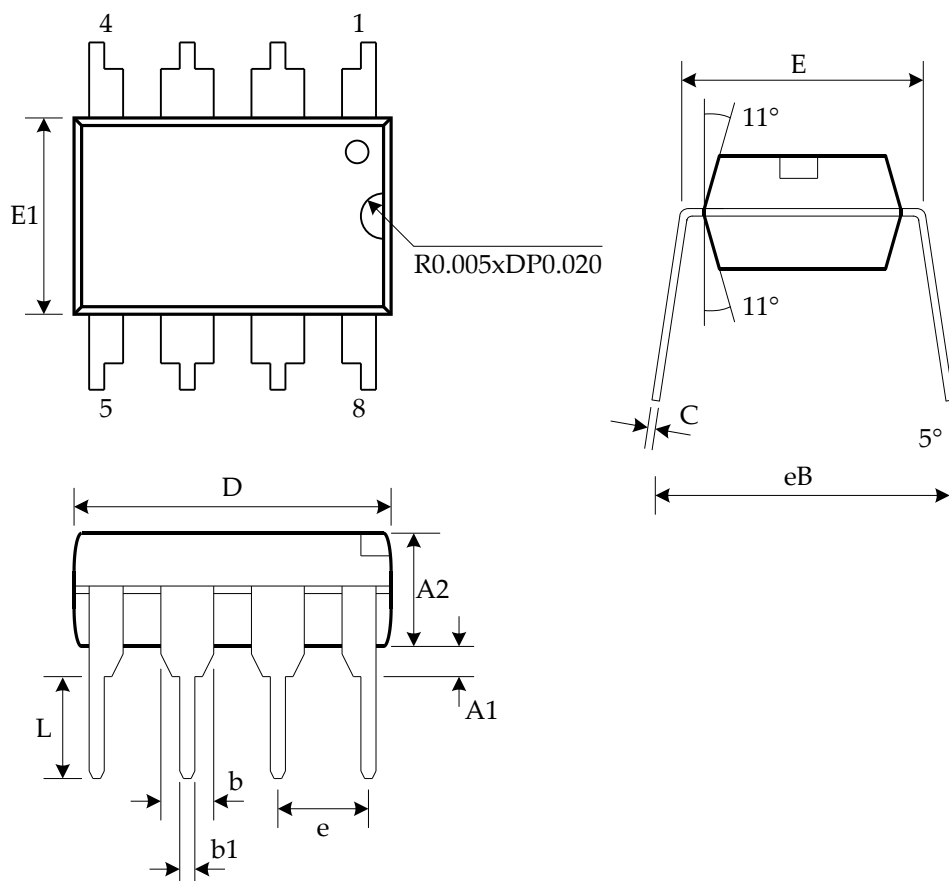


Figure 42: DIP8(300mil) Package

Table 26: The Package Dimensions of DIP8(300mil)

Symbol		A1	A2	b	b1	C	D	E	E1	e	eB	L
Unit												
mm	MIN.	0.38	3.00	1.27	0.38	0.20	9.05	7.62	6.12		7.62	3.04
	NOM.	0.72	3.25	1.46	0.46	0.28	9.32	7.94	6.38	2.54	8.49	3.30
	MAX.	1.05	3.50	1.65	0.54	0.34	9.59	8.26	6.64		9.35	3.56
Inch	MIN.	0.015	0.118	0.050	0.015	0.008	0.356	0.300	0.242		0.333	0.120
	NOM.	0.028	0.128	0.058	0.018	0.011	0.367	0.313	0.252	0.100	0.345	0.130
	MAX.	0.041	0.138	0.065	0.021	0.014	0.378	0.326	0.262		0.357	0.140

Notes:

Package length and width do not include mold flash.

11.5. WSON8 (6*5mm)

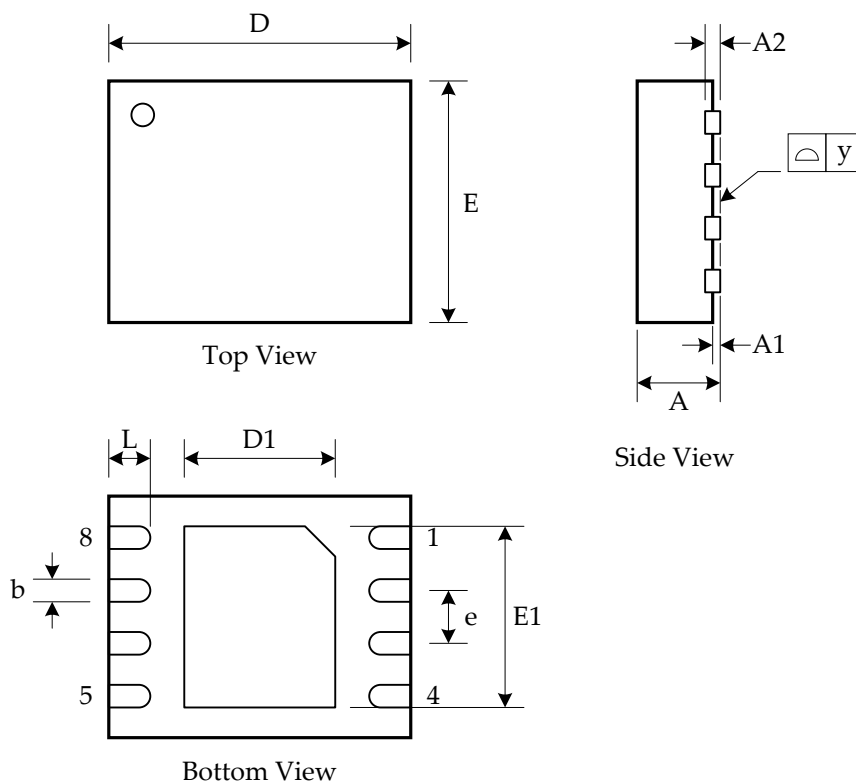


Figure 43: WSON8(6*5mm) Package

Table 27: The Package Dimensions of WSON8(6*5mm)

Symbol		A	A1	A2	b	D	D1	E	E1	e	y	L
Unit												
mm	MIN.	0.70		0.19	0.35	5.90	3.25	4.90	3.85		0.00	0.50
	NOM.	0.75		0.22	0.42	6.00	3.37	5.00	3.97	1.27 BSC	0.04	0.60
	MAX.	0.80	0.05	0.25	0.48	6.10	3.50	5.10	4.10		0.08	0.75
Inch	MIN.	0.028		0.007	0.014	0.232	0.128	0.193	0.151		0.000	0.020
	NOM.	0.030		0.009	0.016	0.236	0.133	0.197	0.156	0.050 BSC	0.001	0.024
	MAX.	0.032	0.002	0.010	0.019	0.240	0.138	0.201	0.161		0.003	0.030

Notes:

1. Package length and width do not include mold flash.
2. The exposed metal pad on the bottom of the package is connected to device ground (GND pin), so that it can either connect to GND or be left floating.

11.6. WSON8 (8*6mm)

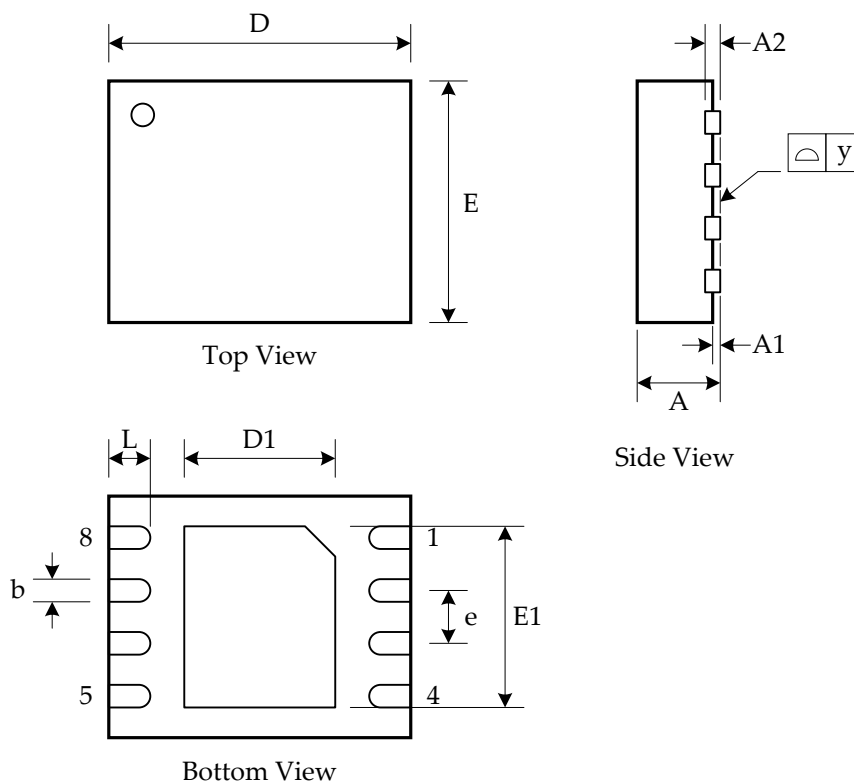


Figure 44: WSON8(8*6mm) Package

Table 28: The Package Dimensions of WSON8(8*6mm)

Symbol		A	A1	A2	b	D	D1	E	E1	e	y	L
Unit												
mm	MIN.	0.70			0.35	7.90	3.25	5.90	4.15		0.00	0.55
	NOM.	0.75		0.20	0.40	8.00	3.42	6.00	4.22	1.27	0.04	0.60
	MAX.	0.80	0.05		0.45	8.10	3.50	6.10	4.40		0.08	0.65
Inch	MIN.	0.028			0.014	0.311	0.128	0.232	0.163		0.000	0.022
	NOM.	0.030		0.008	0.016	0.315	0.135	0.236	0.166	0.050	0.001	0.024
	MAX.	0.032	0.002		0.019	0.319	0.138	0.240	0.173		0.003	0.027

Notes:

1. Package length and width do not include mold flash.
2. The exposed metal pad on the bottom of the package is connected to device ground (GND pin), so that it can either connect to GND or be left floating.

11.7. TFBGA-24(6*4 ball array)

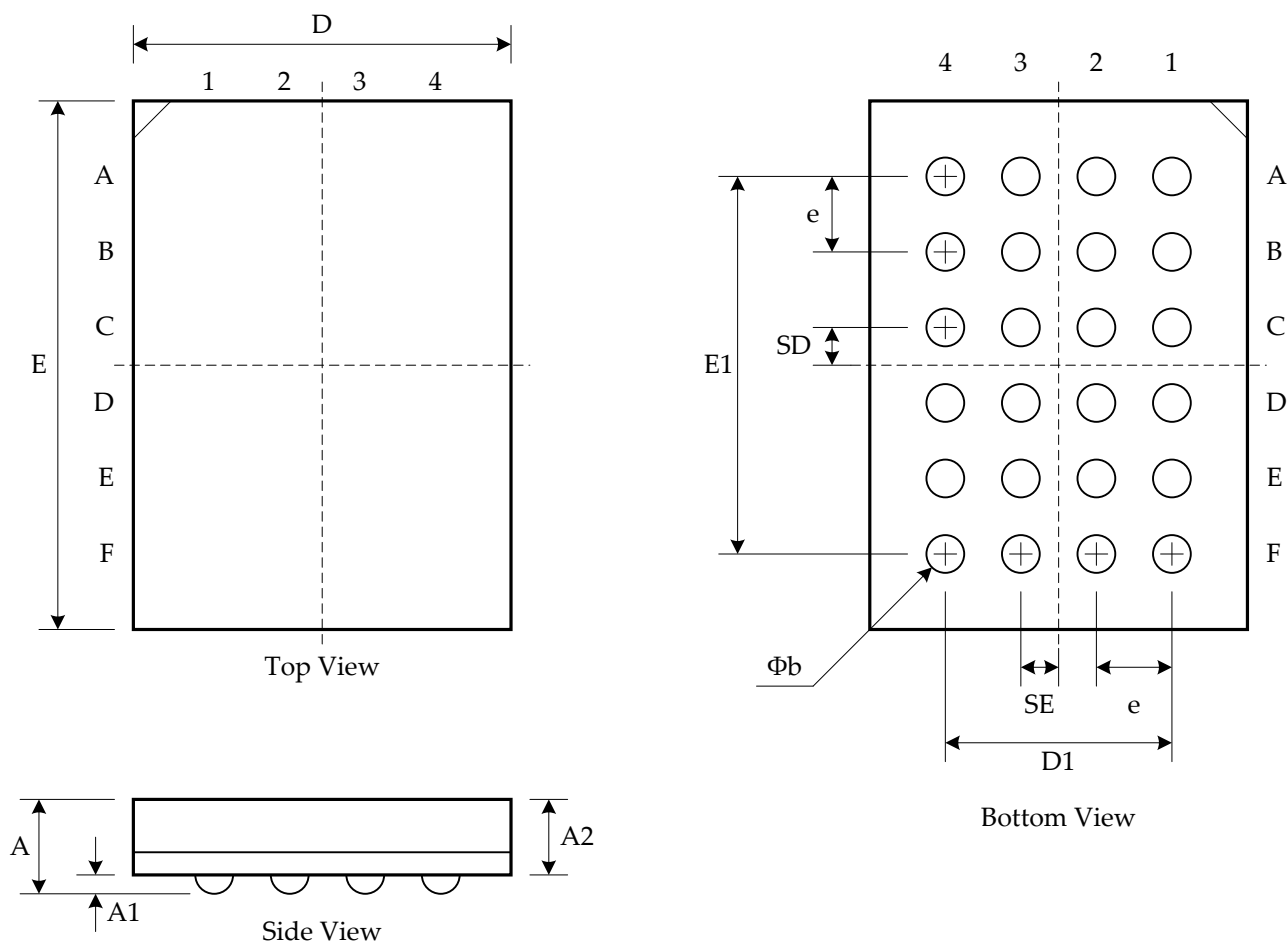


Figure 45: TFBGA-24(6*4 ball array) Package

Table 29: The Package Dimensions of TFBGA-24(6*4 ball array)

Symbol		A	A1	A2	b	D	D1	E	E1	e	SE	SD
Unit												
mm	MIN.		0.25		0.35	5.95	3.00 BSC	7.95	5.00 BSC	1.00 BSC	0.50 TYP	0.50 TYP
	NOM.		0.30	0.85	0.40	6.00		8.00				
	MAX.	1.20	0.35		0.45	6.05		8.05				
Inch	MIN.		0.010		0.014	0.234	0.118 BSC	0.313	0.197 BSC	0.039 BSC	0.020 TYP	0.020 TYP
	NOM.		0.012	0.033	0.016	0.236		0.315				
	MAX.	0.047	0.014		0.018	0.238		0.317				

Notes:

Package length and width do not include mold flash.

11.8. SOP16 (300mil)

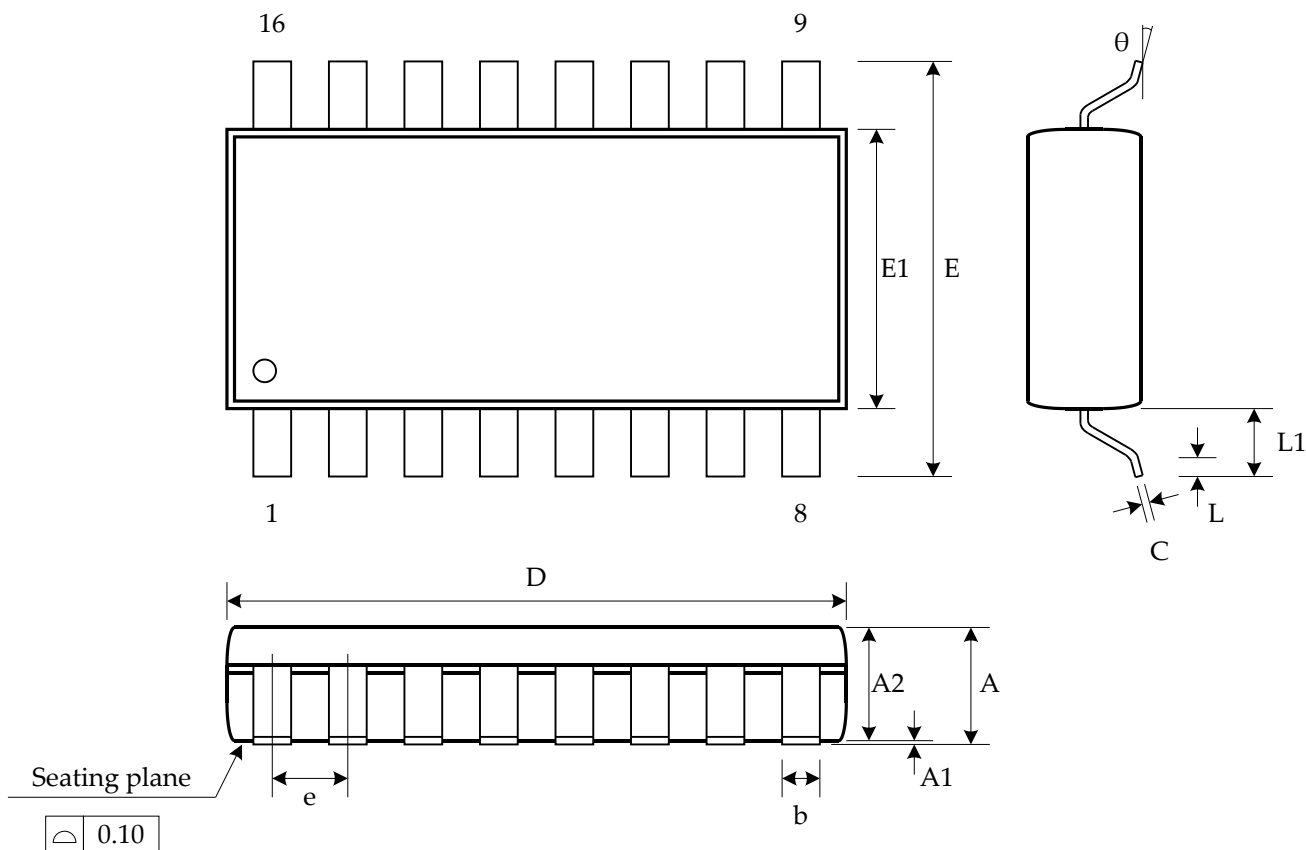


Figure 46: SOP16(300mil) Package

Table 30: The Package Dimensions of SOP16(300mil)

Symbol		A	A1	A2	b	C	D	E	E1	e	L	L1	θ
Unit													
mm	MIN.	2.36	0.10	2.24	0.36	0.20	10.10	10.10	7.42		0.40	1.31	0
	NOM.	2.55	0.20	2.34	0.41	0.25	10.30	10.35	7.52	1.27 BSC	0.84	1.44	5
	MAX.	2.75	0.30	2.44	0.51	0.30	10.50	10.60	7.60		1.27	1.57	8
Inch	MIN.	0.093	0.004	0.088	0.014	0.008	0.397	0.397	0.292		0.016	0.052	0
	NOM.	0.100	0.008	0.092	0.016	0.010	0.405	0.407	0.296	0.050 BSC	0.033	0.057	5
	MAX.	0.108	0.012	0.096	0.020	0.012	0.413	0.417	0.299		0.050	0.062	8

Notes:

1. Package length and width do not include mold flash.
2. Seating plane: Max. 0.10mm.

11.9. USON8 (4*4mm)

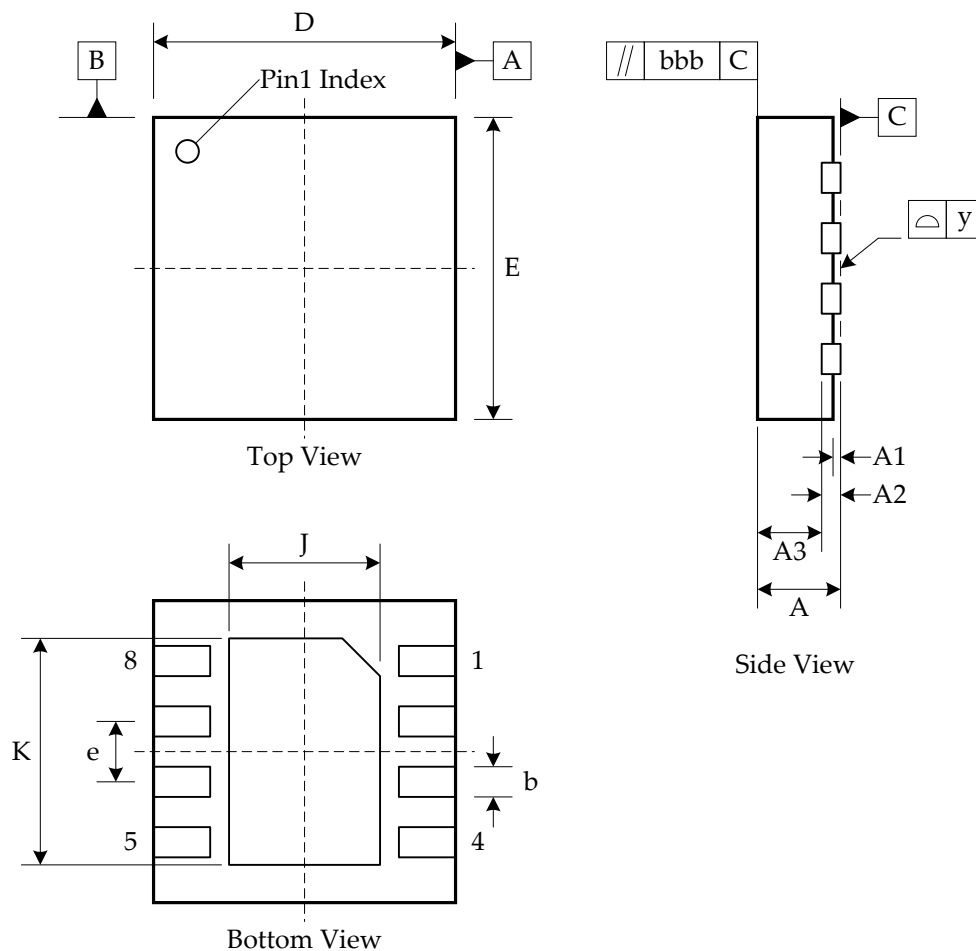


Figure 47: USON8(4*4mm) Package

Table 31: The Package Dimensions of USON8(4*4mm)

Symbol		A	A1	A2	A3	b	D	E	e	J	K	L
Unit												
mm	MIN.	0.40	0.00	0.15 REF	0.25	0.25	3.90	3.90	0.8 BSC	2.20	2.90	0.35
	NOM.	0.45	---		0.30	0.30	4.00	4.00		2.30	3.00	0.40
	MAX.	0.50	0.05		0.35	0.35	4.10	4.10		2.40	3.10	0.45
Inch	MIN.	0.015	0.000	0.15 REF	0.009	0.009	0.153	0.153	0.8 BSC	0.086	0.114	0.013
	NOM.	0.017	---		0.011	0.011	0.157	0.157		0.090	0.118	0.015
	MAX.	0.019	0.001		0.013	0.013	0.161	0.161		0.094	0.122	0.017

Notes:

1. Package length and width do not include mold flash.
2. The exposed metal pad on the bottom of the package is connected to device ground (GND pin), so that it can either connect to GND or be left floating.

11.10. USON8 (4*3mm)

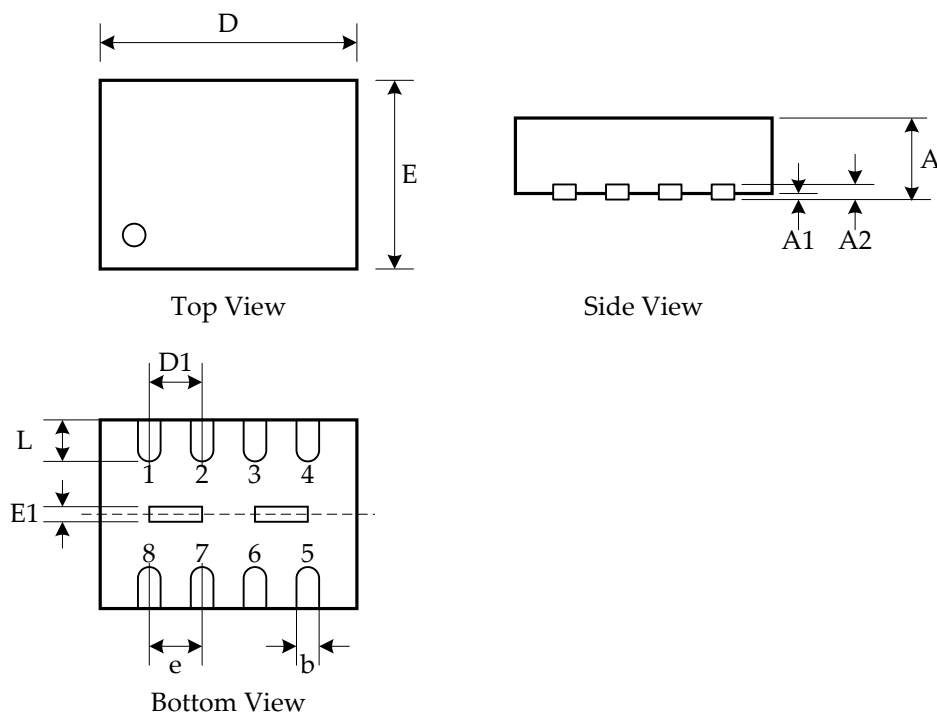


Figure 48: USON8(4*3mm) Package

Table 32: The Package Dimensions of USON8(4*3mm)

Symbol		A	A1	A2	b	D	D1	E	E1	e	L
Unit											
mm	MIN.	0.50	0.00	00	0.25	3.90	0.70	2.90	0.10	0.80 BSC	0.55
	NOM.	0.55	0.02	0.15	0.30	4.00	0.80	3.00	0.20		0.60
	MAX.	0.60	0.05	00	0.35	4.10	0.90	3.10	0.30		0.65
Inch	MIN.	0.020	0.000	00	0.010	0.153	0.027	0.114	0.004	0.31 BSC	0.022
	NOM.	0.022	0.001	0.006	0.012	0.157	0.031	0.118	0.008		0.024
	MAX.	0.024	0.002	00	0.014	0.161	0.035	0.122	0.012		0.026

Notes:

- Package length and width do not include mold flash.
- The exposed metal pad on the bottom of the package is connected to device ground (GND pin), so that it can either connect to GND or be left floating.

11.11. USON8 (2*3mm)

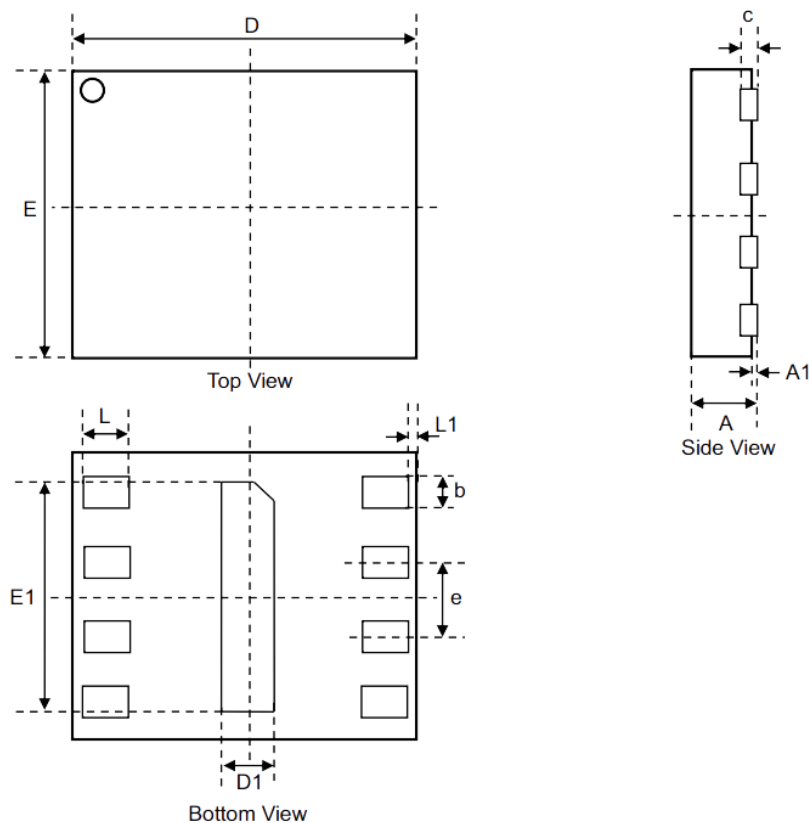


Figure 49: USON8(2*3mm) Package

Table 33: The Package Dimensions of USON8(2*3mm)

Symbol		A	A1	c	b	D	D1	E	E1	e	L	L1
Unit												
mm	MIN.	0.45	0.00	0.10	0.20	2.90	0.15	1.90	1.55	0.50 BSC	0.30	0.05
	NOM.	0.50	0.02	0.15	0.25	3.00	0.20	2.00	1.60		0.35	0.10
	MAX.	0.55	0.05	0.20	0.30	3.10	0.25	2.10	1.65		0.40	0.15
Inch	MIN.	0.018		0.004	0.008	0.114	0.006	0.075	0.061	0.020 BSC	0.012	0.002
	NOM.	0.020	0.001	0.006	0.010	0.118	0.008	0.079	0.063		0.014	0.004
	MAX.	0.022	0.002	0.008	0.012	0.122	0.010	0.083	0.065		0.016	0.006

Notes:

- Package length and width do not include mold flash.
- The exposed metal pad on the bottom of the package is connected to device ground (GND pin), so that itⁱⁱ can either connect to GND or be left floating.

12. Revision History

The table below shows the revision history of this document.

Date	Version	Revision
Oct 15, 2024 ⁱⁱⁱ	v1.0	NeuMem initial release.
Dec 12, 2024	v1.1	Update the Identification list

13. Important Notice

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